

Datasheet

cks32f103x8 cks32f103xb

32-bit ARM core-based standard microcontrollers with 64 or 128K bytes of flash memory

functionality

■Core: ARM 32-bit CortexTM-M3 core

- Up to 72MHz operating frequency, up to
 1.25DMips/MHz at 0 wait-cycle memory access (Dhrystone2.1)
- Single-cycle multiplication and hardware division

■ memory (unit)

- 64KB or 128KB Program Flash
- 20KB SRAM

■Clock, reset and power management

- 2.0 to 3.6 volt power supply and I/O pins
- Power On/Power Off Reset (POR/PDR),
 Programmable Voltage Monitor (PVD)
- 4∼16MHz Crystal Oscillator
- Embedded factory-tuned 8MHz high-speed
 RC oscillator
- Embedded 40kHz low-speed RC oscillator with calibration
- PLL for generating CPU clock
- 32kHz RTC oscillator with calibration function

■Two 12-bit ADCs with 1µs conversion time (up to 16 input channels)

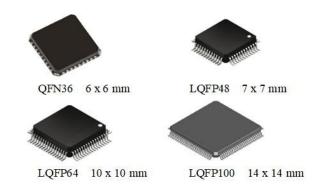
- Conversion range: 0 to 3.6V
- Dual sample and hold function
- temperature sensor

■DMA:

- 7-Channel DMA Controller
- Supported peripherals: Timer, ADC, SPI, I2C and USART

■low power

- Sleep, shutdown and standby modes
- vbat supplies power to the RTC and backup registers



■Up to 80 fast I/O ports

 26/37/51/80 I/O ports, all I/O ports can be mapped to 16 external interrupts; almost all ports can withstand 5V signals

debug mode

- Serial Single Wire Debug (SWD) and JTAG interfaces

■7 timers

- Three 16-bit timers, each with up to four channels for input capture/output compare/PWM or pulse counting and incremental encoder inputs
- 1 x 16-bit PWM Advanced Control Timer with Deadband Control and Emergency Brake for motor control
- 2 watchdog timers (standalone and windowed)
- System time timer: 24-bit self-subtracting counter

■ Up to 9 communication interfaces

- Up to 2 I2C interfaces (SMBus/PMBus support)
- Up to 3 USART interfaces (supports ISO7816 interface, LIN.
 - IrDA interface and modem control)
- Up to 2 SPI interfaces (18M bits/sec)
- CAN interface (2.0B active)
- USB 2.0 Full Speed Interface

■ CRC calculation unit, 96-bit chip unique

CETC 中科芯集成电路有限公司 CHINA KEY SYSTEM & INTEGRATED CIRCUIT CO.,LTD

identifier

CKS32F103x8 and CKS32F103xB, a series of 32-bit MCUs from Semiconductor Manufacturing Corp.



Device

Compari

CKS32F103x8(B) Product Features and Peripheral Configuration

SOn Product Model Peripheral Interface		CKS32F1	03T8/TB CK		KS32F103C8/CB		CKS32F103R8/RB		CKS32F103VB	
Flash memory - K bytes			64	64		64	128	64	128	128
SRAM- K bytes			20)		20			20	20
timed	general		3			3			3	3
(of	purpose									
explosi	Advance	d	1			1			1	1
ve etc)	Controls	;								
tool										
	SPI		1			2			2	2
com	I2C		1			2			2	2
mu	USART		2			3			3	3
nica	USB		1			1			1	1
tion	CAN		1			1	1,	$\langle \cdot \rangle$	1	1
S										
inte							1			
rfac					1. **					
e CDIO r	2011		26	-	1	27			51	80
GPIO p			20))31		J1		80
chann			19			\				
	Synchronoi	1S	2	d's	r -	2			2	2
	r M g Inf umber of	- 1	mativi	nnels	10 channels		ls	16 channels		16 channels
Produ	ct Model	CV	ackage	Numbe	r of	boxed	Ŋuņ	ber of	boxed	cartons
01	nerating	Су	form	trays	S	tray		oxes,		
CKS32	F103T8T6 oltage		QFN36	490PCS/		10 travs/box		PCS/box		on 29400PCS/Carton
	CKS32P103T1BTg6 temperature		QFN36	Amb 490PCS/	— Ambient 490PCS/Tray Ju		t temperature: -/ 10 4900 Inction temperal trays/box		6 boxes/carte	05 C on 29400PCS/Carton
CKS321 Sea	F103C8T6 al inside		LQFP48 QFN	250PCS/ 36	Tray	LQFP48 trays/box	25001	PCS/box _L	6 boxes/carto	on 15000PCS/Carton
CKS32F103CBT6]	LQFP48	250 PCS/	/tray	10 trays/box	25001	PCS/box	6 boxes/carte	on 15000 PCS/box
CKS32F103R8T6]	LQFP64	160 PCS/	plate			PCS/box	6 boxes/carte	on 9600 PCS/box
						trays/box				
CKS32I	F103RBT6]	LQFP64	160 PCS/	disk'	10	1600	PCS/box	6 boxes/carte	on 9600 PCS/box
						trays/box				
	F103VBT6		QFP100	90 PCS/p		10		PCS/box	6 boxes/carte	on 5400 PCS/box
CKS32F103>	«8 and CKS32F	.03x	B, a series of 3	2-bit MCU	s fror	trays/box				

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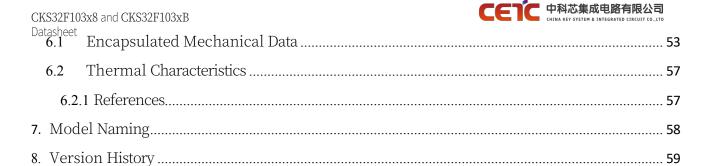


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This document gives the device characteristics of the CKS32F103x8 and CKS32F103xB standard MCU products.

The CKS32F103x8 and CKS32F103xB datasheets must be read in conjunction with their associated reference manuals.

For information about the CortexTM-M3 core, please refer to the Cortex-M3 Technical Reference Manual, available for download from ARM's website:

http://infocenter.arm.com/help/index.jsp?topic=/com.arm.doc.ddi0337e/.





2. Specification

The CKS32F103x8 and CKS32F103xB standard MCU series utilize a high-performance ARM® CortexTM-M3 32-bit RISC core operating at 72MHz, with built-in high-speed memories (up to 128K bytes of Flash and 20K bytes of SRAM), a rich set of enhanced I/O ports, and peripherals connected to two APB buses. Two 12-bit ADCs, three general-purpose 16-bit timers, and a PWM timer are included, along with standard and advanced communication interfaces: up to two I2C and SPI interfaces, three USART interfaces, a USB interface, and a CAN interface.

The CKS32F103x8 and CKS32F103xB standard MCUs are available with supply voltages from 2.0V to 3.6V, an operating temperature range of -40°C to +85°C, and an extended temperature range of -40°C to +105°C, with a range of power-saving modes to ensure that low-power applications are required.

The CKS32F103x8 and CKS32F103xB standard series are available in four different packages ranging from 36 pins to 100 pins; the peripheral configurations in the devices vary depending on the package. A basic description of all the peripherals in this family is given below.

These extensive peripheral configurations enable the CKS32F103x8 and CKS32F103xB standard series microcontrollers to be used in a wide variety of applications:

- Motor drives and application control
- Medical and handheld devices
- PC gaming peripherals and GPS platforms
- Industrial applications: programmable logic controllers (PLCs), inverters, printers and scanners
- Alarm systems, video intercom and HVAC systems, etc.

2.1 summarize

2.1.1 ARM® 's CortexTM-M3 core with embedded Flash and SRAM

ARM's Cortex™-M3 processor is the latest generation of embedded ARM processors, providing the low-cost platform, reduced pin count and reduced system power consumption needed to implement MCUs, while delivering superior computational performance and advanced interrupt system response.

ARM's Cortex™-M3 is a 32-bit RISC processor that provides additional code efficiency, utilizing the high performance of the ARM core in the storage space typically found in 8- and 16-bit systems.

The CKS32F103x8 and CKS32F103xB standard series have a built-in ARM core, so it is compatible with all ARM tools and software. **Error! Unrecognized switch parameters.** This is the functional block diagram of this series.



2.1.2 internal flash memory

 $64 K \ \text{or} \ 128 K$ bytes of internal flash memory for programs and data.



2.1.3 CRC (Cyclic Redundancy Check) calculation unit

The CRC (Cyclic Redundancy Check) calculation unit uses a fixed polynomial generator to produce a CRC code from a 32-bit data word. In numerous applications, CRC-based techniques are used to verify the consistency of data transmission or storage. Within the scope of the EN/IEC 60335-1 standard, which provides a means of detecting errors in flash memory, the CRC calculation unit can be used to compute the signature of software in real time and compare it with the signature generated at the time of linking and generating that software.

2.1.4 Internal SRAM

20K bytes of internal SRAM that can be accessed (read/write) by the CPU with 0 wait cycles.

2.1.5 Nested Vectorized Interrupt Controller (NVIC)

The CKS32F103x8 and CKS32F103xB standard models have a built-in nested vectorized interrupt controller capable of handling up to 43 maskable interrupt channels (excluding 16 CortexTM-M3 interrupt lines) and 16 priority levels.

- Tightly coupled NVICs enable low-latency interrupt response processing
- Interrupt vector entry address directly into the kernel
- Tightly Coupled NVIC Interface
- Allow early processing of interrupts
- Handling late arriving higher priority interrupts
- Support for interrupting the tail link function
- Automatic saving of processor state
- Auto-resume on return from interrupt, no additional instruction overhead required

The module provides flexible interrupt management capabilities with minimal interrupt latency.

2.1.6 External Interrupt/Event Controller (EXTI)

The external interrupt/event controller contains 19 edge detectors for generating interrupt/event requests. Each interrupt line can be independently configured with its trigger event (rising or falling edge or double edge) and can be individually masked; a pending register maintains the status of all interrupt requests. EXTI can detect pulses with a width less than the clock period of the internal APB2. Up to 80 general-purpose I/O ports are connected to 16 external interrupt lines.

2.1.7 Clock and startup

CKS32F103x8 and CKS32F103xB



Datash Prie selection of the system clock is done at startup, the internal 8MHz RC oscillator is selected as the default CPU clock at reset, then an external 4-16MHz clock with failure monitoring can be selected; when an external clock failure is detected, it is isolated and the system automatically switches to the internal RC oscillator, and if interrupts are enabled, the software receives the corresponding interrupts. Similarly, the PLL clock can be fully isolated when needed.



of interrupt management (e.g., when an external oscillator used during a period fails).

Multiple prescalers are used to configure the frequency of the AHB, the high speed APB (APB2), and the low speed APB (APB1) regions. the maximum frequency of the AHB and high speed APB is 72MHz, and the maximum frequency of the low speed APB is 36MHz. refer to the Clock Driver Block Diagram as shown in Figure 2.

2.1.8 bootstrap model

At startup, one of three bootstrap modes can be selected via the bootstrap pin:

- Bootstrap from program flash memory
- Bootstrap from system memory
- Bootstrap from internal SRAM

The bootloader is stored in system memory and can be reprogrammed to flash memory via USART1.

2.1.9 Power supply program

- VDD = 2.0 to 3.6V: The VDD pin powers the I/O pins and the internal regulator.
- VSSA, VDDA = 2.0 to 3.6V: Provides power to the analog portion of the ADC, reset module, RC oscillator, and PLL. Using the ADC
 VDDA must not be less than 2.4 V. VDDA and VSSA must be connected to VDD and VSS respectively.
- VBAT = 1.8 to 3.6V: When VDD is turned off, power is supplied (via the internal power switcher) to the RTC, external 32kHz oscillator, and back-up registers.

For more information on how to connect the power supply pins, see Figure 10 Power Supply Scheme.

2.1.10 Power supply monitor

A power-on reset (POR)/power-down reset (PDR) circuit is integrated into the device, which is always active to ensure that the system operates when the power supply exceeds 2V; when VDD falls below the set threshold (VPOR/PDR), the device is placed in reset without the need for an external reset circuit. The device also includes a programmable voltage monitor (PVD) that monitors the VDD/VDDA supply and compares it to the threshold VPVD, generating an interrupt when VDD falls below or rises above the threshold VPVD, which can be used by the interrupt handler to issue a warning message or to transfer the microcontroller to a safe mode The PVD function needs to be programmed to enable it. Refer to Table 8 for VPOR/PDR and VPVD values.

2.1.11 regulator

The regulator has three modes of operation: main mode (MR), low power mode (LPR) and shutdown





- Main mode (MR) for normal runtime operation
- Low power mode (LPR) for CPU shutdown mode
- Shutdown mode is used in standby mode of the CPU: the output of the regulator is high-resistance, the power supply to the core circuitry is cut off, and the regulator is in a zero-consumption state (but the contents of the registers and SRAM will be lost).

The regulator is always active after reset and shuts down in standby mode at the high resistance output.



2.1.12 Low Power Mode

The CKS32F103x8 and CKS32F103xB standard products support three low-power modes that provide an optimal balance between the requirement for low power consumption, short start-up times and multiple wake-up events.

• sleep mode

In sleep mode, only the MCU is stopped and all peripherals are active and can wake up the MCU in case of an interrupt/event.

shutdown mode

The shutdown mode achieves the lowest power consumption while maintaining no loss of SRAM and register contents. In shutdown mode, all internal 1.5V sections are de-energized, the PLL, the HSI's RC oscillator, and the HSE crystal oscillator are turned off, and the regulator can be placed in either normal mode or low-power mode.

The microcontroller can be woken up from shutdown mode by any signal configured as EXTI, which can be one of the 16 external I/O ports, the output of the PVD, an RTC alarm, or a USB wake-up signal.

standby mode

Minimal power consumption can be achieved in standby mode. The internal voltage regulator is switched off, so that all internal 1.5V sections are disconnected; the PLL, the RC oscillator of the HSI and the HSE crystal oscillator are also switched off; by entering the standby mode, the contents of the SRAM and the registers are lost, but the contents of the backup registers remain, and the standby circuits are still working.

Exiting from standby mode is conditional on an external reset signal on NRST, an IWDG reset, a rising edge on the WKUP pin or a

RTC when the alarm occurs.

NOTE: *The RTC*, *IWDG* and their corresponding clocks are not stopped when entering shutdown or standby mode.

2.1.13 DMA

Flexible 7-way general-purpose DMA manages memory-to-memory, device-to-memory, and memory-to-device data transfers; the DMA controller supports ring buffer management, avoiding interrupts when controller transfers reach the end of the buffer.

Each channel has dedicated hardware DMA request logic, while each channel can be triggered by software; the length of the transmission and the source and destination addresses of the transmission can be set individually by software.

DMA can be used for the main peripherals: SPI, I2C, USART, as well as the general purpose, basic and advanced control timers TIMx and ADC.



2.1.14 RTC (Real Time Clock) and Backup Registers

The RTC and Backup Registers are powered by a switch that selects $_{VDD\ when\ VDD}$ is active, otherwise they are powered by $_{the\ VBAT}$ pin. The back-up registers (10 16-bit registers) can be used to hold 20 bytes of user application data when $_{VDD}$ is turned off. The RTC and back-up registers are not reset by the system or power reset source; nor are they reset when woken up from standby mode.

The real time clock has a set of continuously running counters, a calendar clock function that can be provided by appropriate software, and an alarm interrupt and phase interrupt function. The RTC's drive clock can be a 32.768kHz oscillator using an external crystal, an internal low-power RC oscillator, or a high-speed external clock divided by 128. The internal low-power RC oscillator has a typical frequency of 40kHz. To compensate for deviations from the natural crystal, the RTC can be calibrated by outputting a 512Hz signal. The internal low-power RC oscillator has a typical frequency of 40kHz, and the RTC's clock can be calibrated by outputting a 512Hz signal to compensate for deviations in the natural crystal.



for long time measurements. There is a 20-bit prescaler for the time base clock, which by default generates a 1-second long time reference when the clock is 32.768kHz.

2.1.15 Timers and Watchdogs

The CKS32F103x8 and CKS32F103xB standard series include 1 advanced control timer, 3 general timers, and

2

The watchdog timer and 1 system timer.

The following table compares the functions of the Advanced Control

Timer, Normal Timer, and Basic Timer:

Table 1 Comparison of Timer Functions

	timers	Counter	Counter	presharing	Generate DMA please	Capture/Compa	compleme	Ì
		Resolution	Туре	factor	look for	re Channel	ntary	
							output	I
	TIM1	16-bit	Incremental count/	Between 1 and 65536	possible	4	there are	Ì
			count	any integer	XX			
	\ 	od Control Ti	down	of	ZZ X 3			ı
F		ed Control Ti	mer (11M1)	Anyinteger				Ì
	ттмыеа	dvan &&dit ontro	l timer (TIM1) can be thought	of as &Mree-ph	ase PWM genera	torhassigne	d to
	TIM4 _{ch}	annels with cor	nplementary	de adbás53ín sert	ion.			Ī
1	he PWM	output can also		complete genera	l-purpose timer.	4 independent c	hannels are	<u> </u>
а	vailable:		ental					

- İnput Capture
- Output Comparison
- Generate PWM (edge or center alignment mode)
- Single pulse output

When configured as a 16-bit standard timer, it has the same function as TIMx timer. When configured as a 16-bit PWM generator, it has full modulation capability (0~100%).

In debug mode, the counter can be frozen while the PWM outputs are disabled, thus cutting off the switches controlled by these outputs.

Many of the functions are the same as the standard TIM timer and the internal structure is the same, so the Advanced Control Timer can operate in concert with the TIM timer through the Timer Link function to provide synchronization or event linking functions.

Universal Timer (TIMx)

Up to three standard timers (TIM2, TIM3, and TIM4) that can run synchronously are built into the CKS32F103x8 and CKS32F103xB standard models. Each timer has a 16-bit auto-loading increment/decrement counter, a 16-bit prescaler, and four independent channels, each of which can be used for input capture, output compare, PWM, and single-pulse mode outputs,

CKS32F103x8 and CKS32F103xB



pates filling up to twelve input capture, output compare, or PWM channels in the largest package configuration.

They can also work with advanced control timers through the timer linking feature, providing synchronization or event linking. The counters can be frozen in debug mode. Any of the standard timers can be used to generate PWM outputs. Each timer has an independent DMA request mechanism.

These timers are also capable of handling signals from incremental encoders, as well as digital outputs from 1 to 3 Hall sensors.



Independent Watchdog

The Standalone Watchdog is based on a 12-bit decrement counter and an 8-bit prescaler, which is clocked by an internal independent 40kHz RC oscillator; since this RC oscillator is independent of the main clock, it can operate in shutdown and standby modes. It can be used as a watchdog to reset the entire system in the event of a problem, or as a free timer to provide timeout management for applications. The option byte can be configured to be a software or hardware initiated watchdog. In debug mode the counter can be frozen.

Windows Watchdog

The window watchdog contains a 7-bit decrement counter that can be configured to run freely. When used as a watchdog, it can reset the entire system in the event of a problem. It is driven by the master clock and has an early warning interrupt; the counter can be frozen in debug mode.

system time base timer

This timer can be used exclusively for real-time operating systems or as a standard decrementing counter. It has the following characteristics:

- 24-bit Decrement Counter
- Auto Reload Function
- Generates a maskable system interrupt when the counter is 0.
- Programmable Clock Source

2.1.16 I2C bus

Up to 2 I² C bus interfaces, capable of operating in multi-master or slave mode, supporting standard and fast modes.

The I2C interface supports 7-bit or 10-bit addressing, and the 7-bit slave mode supports dual slave address addressing. A hardware CRC generator/checker is built-in. The interface can be operated using DMA and supports SMBus bus version 2.0/PMBus bus.

2.1.17 Universal Synchronous/Asynchronous Transceiver (USART)

The USART1 interface communicates at rates up to 4.5 Mb/s, while the other interfaces communicate at rates up to Mb/s. The USART interface has hardware CTS and

RTS signal management, support for IrDA SIR ENDEC transmission codecs, ISO7816-compatible smart cards and LIN master/slave functionality. All USART interfaces can be operated using DMA.

2.1.18 Serial Peripheral Interface (SPI)

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Datash to 2 SPI interfaces, configurable in slave or master mode, with full- and half-duplex communication rates up to 18 Mb/s. 3-bit prescaler generates 8 master mode frequencies, configurable in 8- or 16-bit data frame format. Hardware CRC generation/checksum support for basic SD card and MMC modes.

DMA operation is available for all SPI interfaces.



2.1.19 Controller Area Network (CAN)

The CAN interface is compatible with specifications 2.0A and 2.0B (active) at bit rates up to 1 Mb/s. It can receive and send standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has 3 transmit mailboxes and 2 receive FIFOs with 3 stages and 14 adjustable filters.

2.1.20 Universal Serial Bus (USB)

The CKS32F103x8 and CKS32F103xB standard series embed a full-speed USB-compatible device controller that follows the full-speed USB device (12 Mb/s) standard, with software-configurable endpoints and standby/wakeup functionality. The USB-specific 48 MHz clock is generated directly from the internal master PLL (clock source must be an HSE crystal oscillator). The 48MHz clock dedicated to USB is generated directly from the internal master PLL (clock source must be an HSE crystal oscillator).

2.1.21 General Purpose Input Output Interface (GPIO)

Each GPIO pin can be configured by software as an output (push-pull or open-drain), an input (pull-up or pull-down or float), or a multiplexed peripheral function port. Most GPIO pins are shared with digital or analog multiplexed peripherals. In addition to having analog input capabilities, all GPIO pins allow high currents to pass.

Where required, the peripheral functions of the I/O pins can be locked by a specific operation to avoid accidental write operations to the I/O registers. The I/O pins on the APB2 can be flipped at speeds up to 18MHz.

2.1.22 ADC (analog/digital converter)

The CKS32F103x8 and CKS32F103xB standard models incorporate two 12-bit analog/digital converters (ADCs), each of which shares up to 16 external channels, and can perform either single conversion or scan mode conversion. In scan mode, conversion can be performed automatically on a selected set of analog input pins.

Other logic functions on the ADC interface include:

- Synchronized sample and hold
- Cross sampling and hold
- Single Sampling

The ADC can be operated using DMA.

The analog watchdog is able to monitor one, multiple or all selected channels with great precision, and generates an interrupt when the monitored signal exceeds a preset threshold.

Events generated by the standard timer (TIMx) and the advanced control timer (TIM1) can CKS32F103x8 and CKS32F103xB, a series of 32-bit MCUs from Semiconductor Manufacturing Corp.

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Beinternally cascaded to the ADC's Start Trigger and Injection Trigger, respectively, and the application program can synchronize the AD conversion with the clock.



2.1.23 temperature sensor

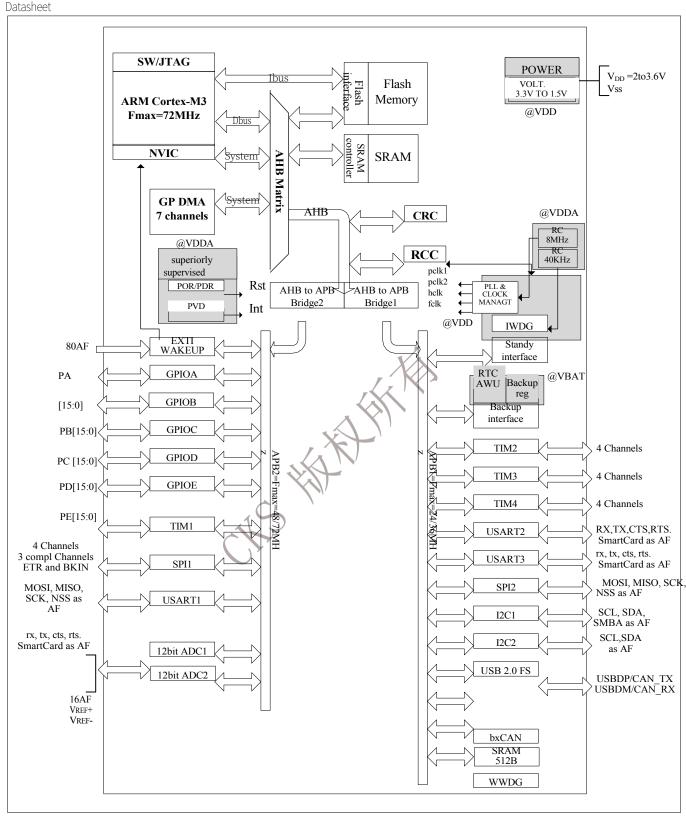
The temperature sensor generates a voltage that varies linearly with temperature over a conversion range of 2V < VDDA< 3.6V. The temperature sensor is internally connected to the input channel of ADC12 IN16, which is used to convert the sensor output to a digital value.

2.1.24 Serial Single Wire JTAG Debug Port (SWJ-DP)

Embedded ARM's SWJ-DP interface, which is a combination of JTAG and serial single-wire debugging interface that enables the connection of either the serial single-wire debugging interface or the JTAG interface. the TMS and TCK signals of the JTAG share the same pins as the SWDIO and SWCLK, respectively, and a special sequence of signals on the TMS pin is used to toggle between the JTAG-DP and the SW-DP.







peripheral function pin

- I. Operating temperature: -40° C to $+105^{\circ}$ C, junction temperature up to 125° C.
- 2. AF: I/O port that can be used as a

CKS32F103x8 and CKS32F103xB Fig. 1 Block diagram of system modules



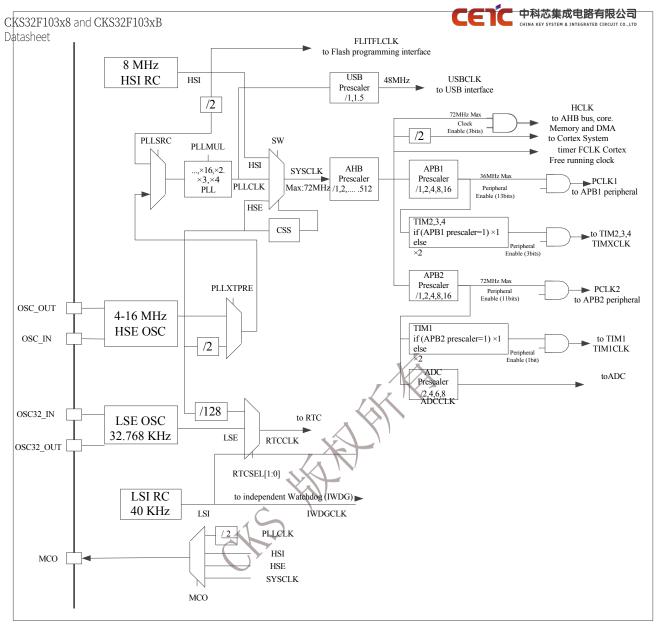


Figure 2 Clock tree

- 1. When the HSI is used as an input to the PLL clock, the maximum system clock frequency can only be 64MHz.
- 2. When using the USB function, both HSE and PLL must be used and the CPU frequency must be 48MHz or 72MHz.
- 3. When an ADC sampling time of 1µs is required, APB2 must be set at 14MHz, 28MHz, or 56MHz.



3. Pin Definitions

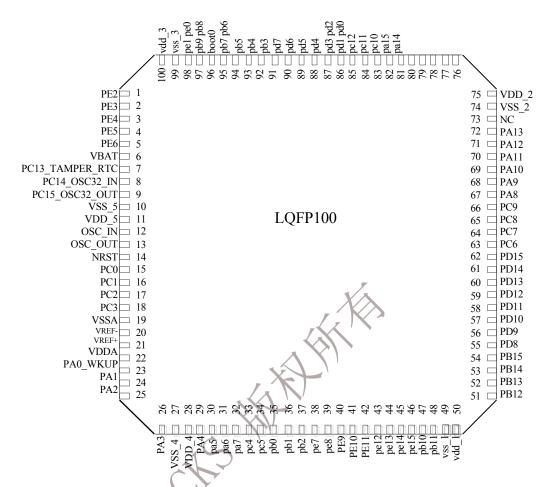


Figure 3CKS32F103xx Standard LQFP100 Pinouts



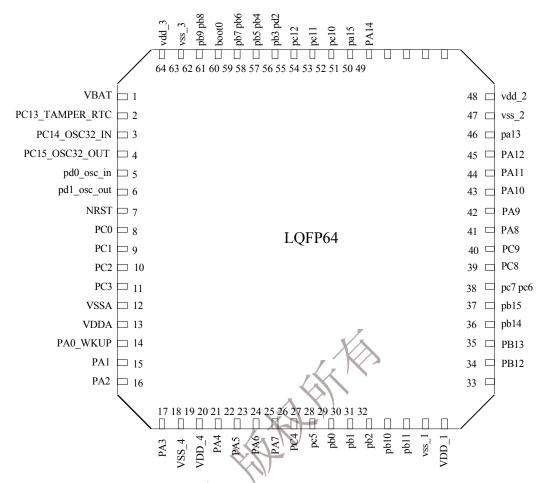


Figure 4CK\$32F103xx Standard LQFP64 Pinout



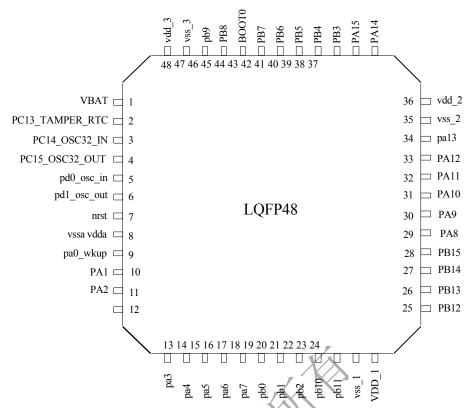


Figure 5CKS32F103xx Standard LQFP48 Pinouts

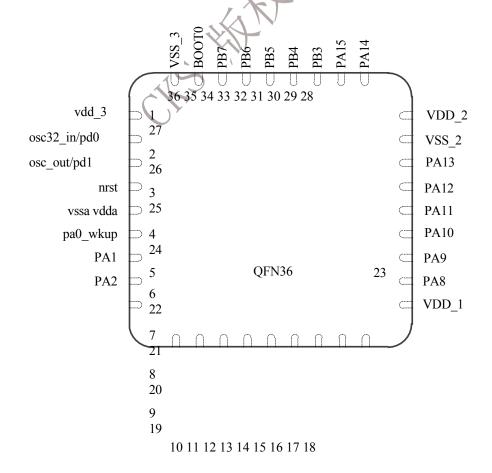




Figure 6CKS32F103xx Standard QFN36 Pinouts



Table 2CKS32F103xx Pin Definitions

	Pin Number			Pin Name	ty	1/O 5	Main	Ontiona	l multiplexing
LQFP48	LQFP64	LQFP100	QFN36	r III Maine	ty p o gy	p o wer le ve l (e le c.)	Function s ⁽³⁾ (after reset)	function	1 0
-	-	1	-	PE2	I/O	FT	PE2	TRACECK	
-	-	2	-	PE3	I/O	FT	PE3	TRACED0	
-	-	3	-	PE4	I/O	FT	PE4	TRACED1	
-	-	4	-	PE5	I/O	FT	PE5	TRACED2	
-	-	5	-	PE6	I/O	FT	PE6	TRACED3	
1	1	6	-	VBAT	S		VBAT		
2	2	7	-	PC13-TAMPER- RTC ⁽⁴⁾	I/O		PC13	TAMPER-RTC	
3	3	8	-	PC14- OSC32_IN ⁽⁴⁾	I/O		PC14	OSC32_IN	
4	4	9	-	PC15- OSC32_OUT ⁽⁴⁾	I/O		PC15	OSC32_OUT	
-	-	10	-	VSS_5	S	7	VSS_5		
-	-	11	-	VDD_5	S		VDD_5		
5	5	12	2	OSC_IN_	I		OCS_IN		PD0 ⁽⁷⁾
6	6	13	3	OSC_OUT	0		OSC_OUT		PD1 ⁽⁷⁾
7	7	14	4	NRST	I/O		NRST		
-	8	15	-	PC0	I/O		PC0	ADC12_IN10	
-	9	16	-	PC1	I/O		PC1	ADC12_IN11	
-	10	17	-	PC2	I/O		PC2	ADC12_IN12	
-	11	18	-	PC3	I/O		PC3	ADC12_IN13	
8	12	19	5	VSSA	S		VSSA		
-	-	20	-	VREF-	S		VREF-		
-	-	21	-	VREF+	S		VREF+		
9	13	22	6	VDDA	S		VDDA		
10	14	23	7	PA0-WKUP	I/O		PA0	WKUP/USART2_C TS ⁽⁶⁾ /ADC12_IN0/ TIM2_CH1_ETR ⁽⁶⁾	
11	15	24	8	PA1	I/O		PA1	USART2_RTS ⁽⁶⁾ / ADC12_IN1/ TIM2_CH2 ⁽⁶⁾	
12	16	25	9	PA2	I/O		PA2	USART2_TX ⁽⁶⁾ /AD c12_in2/tim2_ch 3 ⁽⁶⁾	
	3x8 and du&for i			series of 32-bit MCU Corp. PA3	s from I/O		PA3	USART2_RX ⁽⁶⁾ /AD C12_IN3/TIM2_CH	



Datasheet						ı				
	Pin Number				4	I/C				
LQFP48	LQFP64	LQFP100	QFN36	Pin Name	ty pæo gy	I/O po vs) er le ve l (e le c.)	Main Function s ⁽³⁾ (after reset)	Optiona functior	l multiplexing	
								4(6)		
-	18	27	-	VSS_4	S		VSS_4			
-	19	28	-	VDD_4	S		VDD_4			
14	20	29	11	PA4	I/O		PA4	spi1_nss ⁽⁶⁾ / usart2_ck / ⁽⁶⁾ ADC12_IN4		
15	21	30	12	PA5	I/O		PA5	SPI1_SCK / ⁽⁶⁾ ADC12_IN5		
16	22	31	13	PA6	I/O		PA6	SPI1_MISO ⁽⁶⁾ / ADC12_IN6/ TIM3_CH1 ⁽⁶⁾	TIM1_BKIN	
17	23	32	14	PA7	I/O		PA7	SPI1_MOSI ⁽⁶⁾ / ADC12_IN7/ TIM3_CH2 ⁽⁶⁾	TIMI_CHIN	
-	24	33	-	PC4	I/O	/	PC4	ADC12_IN14		
-	25	34	-	PC5	I/O	·X	PC5	ADC12_IN15		
18	26	35	15	PB0	I/O	A.	PB0	ADC12_IN8/ TIM3_CH3 ⁽⁶⁾	TIM1_CH2N	
19	27	36	16	PB1	J/O	\	PB1	ADC12_IN9/ TIM3_CH4 ⁽⁶⁾	TIM1_CH3N	
20	28	37	17	PB2	I/O	FT	PB2/ BOOT1			
-	-	38	-	PE7	I/O	FT	PE7		TIM1_ETR	
-	-	39	-	PE8	I/O	FT	PE8		TIM1_CH1N	
-	-	40	-	PE9	I/O	FT	PE9		TIM1_CH1	
-	-	41	-	PE10	I/O	FT	PE10		TIM1_CH2N	
-	-	42	-	PE11	I/O	FT	PE11		TIM1_CH2	
-	-	43	-	PE12	I/O	FT	PE12		TIM1_CH3N	
-	-	44	-	PE13	I/O	FT	PE13		TIM1_CH3	
-	-	45	-	PE14	I/O	FT	PE14		TIM1_CH4	
-	-	46	-	PE15	I/O	FT	PE15		TIM1_BKIN	
21	29	47	-	PB10	I/O	FT	PB10	I2C2_SCL/ USART3_TX ⁽⁶⁾	TIM2_CH3	
22	30	48	-	PB11	I/O	FT	PB11	I2C2_SDA/ USART3_RX ⁽⁶⁾	TIM2_CH4	

 CKS32F103x8 and CKS32F103xB

 Data如此
 31
 49
 18
 VSS_1
 S
 VSS_1

 24
 32
 50
 19
 VDD_1
 S
 VDD_1

CETC 中科芯集成电路有限公司

Datasheet Pin Number O/Ity pdo Main p Pin Name Optional multiplexing LQFP100 LQFP48 LQFP64 QFN36 Function function VV3 er gy $S^{(3)}$ le ve l (after (e le reset) c. SPI2 NSS/ I2C2 SMBAI/ PB12 I/O PB12 25 33 51 FT USART3 CK /(6) TIM1 BKIN(6) SPI2_SCK/ 34 52 **PB13** I/O FT**PB13** 26 USART3 CTS(6) / $TIM1_CH1N^{(6)}$ SPI2 MISO/ 27 35 53 PB14 I/O FT PB14 USART3 CTS(6) / $TIM1_CH2N^{(6)}$ SPI2 MOSI/ 28 36 54 **PB15** I/O FT **PB15** TIM1 CH3N(6) PD8 I/O FT PD8 USART3 TX 55 PD9 56 PD9 I/O FT USART3 RX PD10 -57 -PD10 I/O FT USART3_CK _ I/O FT PD11 58 PD11 USART3 CTS TIM4_CH1/ I/O FT 59 PD12 PD12 USART3 RTS PD13 I/O FT PD13 TIM4_CH2 60 _ 1/0 61 PD14 FT PD14 TIM4 CH3 _ _ PD15 62 I/O FT PD15 TIM4 CH4 37 63 PC6 I/O FT PC6 TIM3 CH1 38 64 PC7 I/O FT PC7 TIM3_CH2 39 65 PC8 I/O FT PC8 TIM3 CH3 40 66 PC9 I/O FT PC9 TIM3 CH4 USART1 CK/ I/O 29 41 67 20 PA8 FT PA8 TIM1 CH1(6)/MCO USART1 TX /(6) 42 I/O FTPA9 30 68 21 PA9 TIM1 CH2(6) USART1_RX /(6) 43 31 69 22 PA10 I/O FT PA10 TIM1 CH3(6) USART1_CTS/ 32 70 23 I/O FT 44 PA11 PA11 USBDM/CANRX(6) /TIM1 CH4(6)

CKS32F	CKS32F103x8 and CKS32F103xB CEIC 中科心集成电路有限公司 CKS32F103xB CEINa Rey System & INTEGRATED CIRCUIT CO.,LT											
Datashe	et							usart1_rts/				
33	45	71	24	PA12	I/O	FT	PA12	usbdp/cantx /(6)				
								TIM1_ETR ⁽⁶⁾				

Datasheet



Datasheet							-		
Pin Number				ts7	I/O				
LQFP48	LQFP64	LQFP100	QFN36	Pin Name	ty Pdo Sy	power le ve l (e e c.)	Main Function s ⁽³⁾ (after reset)	Optional multiplexing function	
34	46	72	25	PA13	I/O	FT	JTMS/SWD IO		PA13
-	-	73	-				unconne	cted	
35	47	74	26	VSS_2	S		VSS_2		
36	48	75	27	VDD_2	S		VDD_2		
37	49	76	28	PA14	I/O	FT	JTCK/ SWCLK		PA14
38	50	77	29	PA15	I/O	FT	JTDI		TIM2_CH1_ETR PA15/SPI1_NSS
-	51	78	-	PC10	I/O	FT	PC10		USART3_TX
-	52	79	-	PC11	I/O	FT	PC11		USART3_RX
-	53	80	-	PC12	I/O	FT	PC12		USART3_CK
		81	2	PD0	I/O	FT	OSC_IN(8)	>	CANRX
		82	3	PD1	I/O	FT	OSC_OUT ⁽⁸		CANTX
-	54	83	-	PD2	I/O	FT	PD2	TIM3_ETR	
-	-	84	-	PD3	I/Q	FT	PD3		USART2_CTS
-	-	85	-	PD4	I/O	FT	PD4		USART2_RTS
-	-	86	-	PD5	I/O	FT	PD5		USART2_TX
-	-	87	-	PD6	I/O	FT	PD6		USART2_RX
-	-	88	-	PD7	I/O	FT	PD7		USART2_CK
39	55	89	30	PB3	I/O	FT	JTDO		pb3/traceswo/ tim2_ch2/ SPI1_SCK
40	56	90	31	PB4	I/O	FT	JNTRST		PB4/TIM3_CH1/ SPI1_MISO
41	57	91	32	PB5	I/O		PB5	I2C1_SMBAI	TIM3_CH2/ SPI1_MOSI
42	58	92	33	PB6	I/O	FT	PB6	I2C1_SCL / ⁽⁶⁾ TIM4_CH1 ⁽⁶⁾	USART1_TX
43	59	93	34	PB7	I/O	FT	PB7	I2C1_SDA / ⁽⁶⁾ TIM4_CH2 ⁽⁶⁾	USART1_RX
44	60	94	35	BOOT0	I		BOOT0		
45	61	95	-	PB8	I/O	FT	PB8	TIM4_CH3 ⁽⁶⁾	I2C1_SCL/ CANRX

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 Datasheet 46
 62
 96
 P89
 I/O
 FT
 P89
 TIM4_CH4(6)
 I2C1_SDA/CANTX

Datasheet



	Pin	Numb	er		t 7	I/O			
LQFP48	LQFP64	LQFP100	QFN36	Pin Name	ty pol o gy	powerle ve le c.	Main Function s ⁽³⁾ (after reset)	Optiona function	nl multiplexing
-	-	97	-	PE0	I/O	FT	PE0	TIM4_ETR	
-	-	98	-	PE1	I/O	FT	PE1		
47	63	99	36	VSS_3	S		VSS_3		
48	64	100	1	VDD_3	S		VDD_3		

- 1. I = Input, O = Output, S = Supply
- 2. FT: 5V Voltage Tolerance
- 3. The PC13, PC14 and PC15 pins are powered by a power switch that can only absorb a limited amount of current (3mA). Therefore, these three pins have the following limitations when used as output pins: when used as output pins, they can only be operated in 2MHz mode, the maximum drive load is 30pF, and they cannot be used as a current source (e.g., to drive LEDs).
- 4. These pins are in the primary functional state when the backup area is first powered up, after that, even if reset, the state of these pins is controlled by the backup area registers (these registers are not reset by the primary reset system) For specific information on how to control these IO ports, refer to the relevant sections of the CKS32F103x8 and CKS32F103xB Reference Manuals for the Battery Backup Area and BKP registers.
- 5. This type of multiplexing can be configured by software to other pins (if available for the corresponding package model), for details please refer to CKS32F103x8 and
 - The Multiplexing Functions I/O chapter and the Debug Setup chapter of the CKS32F103xB Reference Manual.
- 6. Pins 2 and 3 for the QFN36 package, and pins 5 and 6 for the LQFP48 and LQFP64 packages are configured as OSC_IN and OSC_OUT function pins by default after a chip reset. Software can reset these pins to function as PD0 and PD1. However, for LQFP100 package, since PD0 and PD1 are intrinsic functional pins, there is no need to reimage them by software. For more details, please refer to the Multiplexed Function I/O section and Debug Setup section of the CKS32F103x8 and CKS32F103xB Reference Manuals. In output mode, PD0 and PD1 can only be configured for 50MHz output mode.
- 7. ADC12_INx (x represents an integer between 0 and 15), which appears in the pin name labeling in the table, indicates that this pin can be ADC1_INx or ADC2_INx. e.g. ADC12_IN9 indicates that this pin can be configured as ADC1_IN9 or ADC2_IN9.
- 8. TIM2_CH1_ETR in the multiplexing function corresponding to pin PA0 in the table indicates that the function can be configured as TIM2_TI1 or TIM2_ETR. Similarly, PA15
 - The name of the corresponding remapping multiplexing function, TIM2 CH1 ETR, has the same meaning.



4. memory image

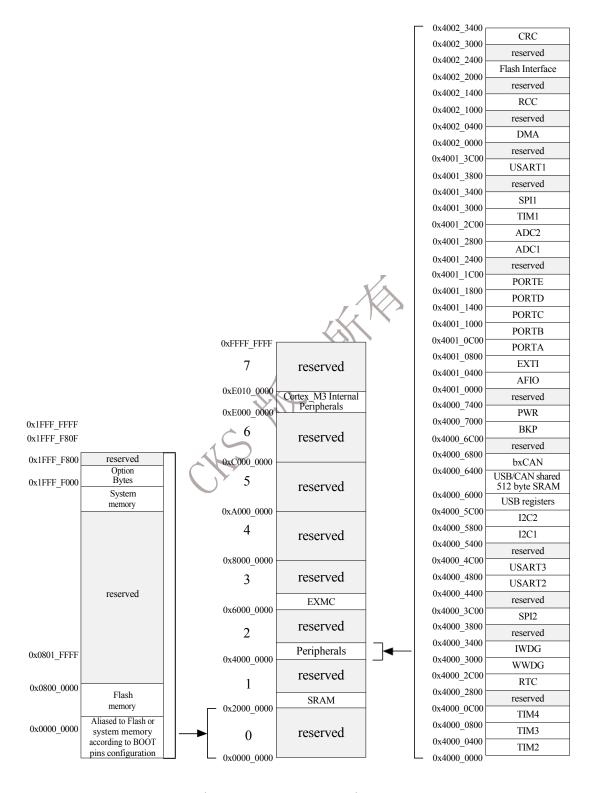


Figure 7 Memory MAP Diagram



5. Electrical Characteristics

5.1 test condition

All voltage's are referenced to vss unless otherwise noted.

5.1.1 Minimum and maximum values

Unless otherwise stated, all minimum and maximum values are guaranteed at the worst case ambient temperature, supply voltage and clock frequency conditions by testing 100% of the product on the production line at an ambient temperature of TA=25°C and $_{TA}$ =TAmax (TAmax matches the selected temperature range).

In the notes below each table, it is stated that the data obtained through comprehensive evaluation, design simulation and/or process characterization will not be tested on the production line; on the basis of the comprehensive evaluation, the minimum and maximum values are obtained by taking the average of the samples tested plus or minus three times the standard distribution (mean $\pm 3\Sigma$).

5.1.2 Typical values

Typical data is based on TA=25°C and $_{VDD}$ =3.3V (2V \leq $_{VDD}$ \leq 3.3V voltage range) unless otherwise noted. These data are for design guidance only and have not been tested.

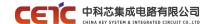
Typical ADC accuracy values are obtained by sampling a standardized batch, tested over all temperature ranges, with 95% of the products having an error less than or equal to the value given ($\pm 2\sum$ on average).

5.1.3 typical curve

Typical curves are for design guidance only and are untested unless otherwise noted.

5.1.4 load capacitance

The load conditions for measuring the pin parameters are shown in Figure 8.



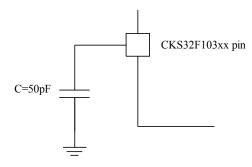


Figure 8 Load Conditions for Pins

5.1.5 Pin Input Voltage

The measurement of the input voltage on the pins is shown in Figure 9.

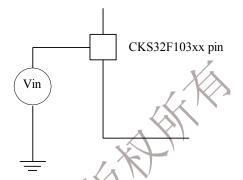


Figure 9 Pin Input Voltage



5.1.6 Power supply program

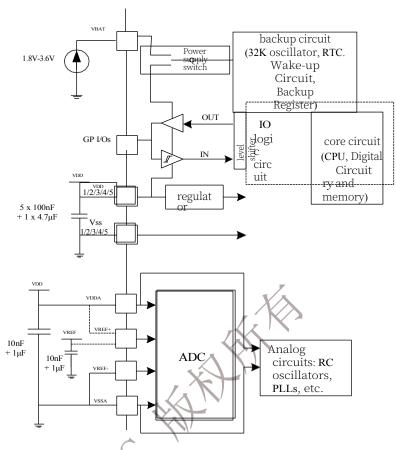


Figure 10 Power supply scheme

Note: The $4.7\mu F$ capacitor in the above diagram must be connected to VDD3.

5.1.7 Current consumption measurement

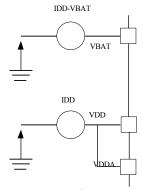


Figure 11 Current consumption measurement scheme



VDD +4.0

vss-0.3

5.2 Absolute maximum rating

Loads applied to the device in excess of the values given in the Absolute Maximum Ratings lists (Tables 3, 4, 5) may cause permanent damage to the device. The fact that only the maximum loads that can be withstood are given does not imply that the device operates functionally without error under these conditions. Prolonged operation of the device at the maximum value will affect the reliability of the device.

notation	descriptive	minimum	maximum	unit
		value	values	(of
				meas
				ure)
VDD - VSS	External mains supply voltage	-0.3	4.0	
	(including _{VDDA} and _{VDD}) (1)			V

Table 3 Voltage Characteristics

1. All power (vdd, vdd) and element (est) vssa) pins must always be connected to the external permissible range power supply system. Input voltage on other pins (2) vss -0.3 4.0

Input voltage on pins with 5V

2. IINJ(PIN) must provided Woltage (differblace), between different bes not exceed its not inverse is not exceed its not inverse inverse inverse inverse inverse inverse inverse inverse inverse injection current; when vinverse inverse injection current.

VESD (HBM)	ESD Electrostatic distralage Cultaget (haract&est&	exction 5.3	.11.
notation	(human body modelescriptive		maximu	unit
	* * * * * * * * * *		m	(of
	15		values	meas
				ure)
IVDD	Total current (supply current) throug	gh the	150	
	VDD/VDDA power supply line (1)			
IVSS	Total current (outgoing current) thro	ough the vss	150	
	ground (¹)			mA

- 1. All power (VDD 1180DA) an Output sink surpristrous and I/O land control pins extern 5 per missible range power supply system.

 Output current on arbitrary I/O and control pins -25
- 2. Independent of the state of
- 3. Reverse current injection can interfere with the analog performance of the device. See Section 5.3.17.
- 4. When several I/O ports have injected currents at the same time, the maximum value of $\sum_{\text{IINJ(PIN)}}$ is the sum of the instantaneous absolute values of the forward injection current and the reverse injection current. This result is based on the characterization of the maximum value of $\sum_{\text{IINJ(PIN) on the}} 4$ I/O ports of the device.



Table 5 Temperature Characteristics

		i atare craracteriot	
notation	descriptive	numerical value	unit (of measure)
TSTG	Storage	-65~+150	°C
	temperature		
	range		
TJ	Maximum	150	°C
	Junction		
	Temperature		



5.3 working conditions

5.3.1 General working conditions

Table 6 General working conditions

	notation	parameters	pr	erequisite		maximu m values	unit (of meas	
	fHCLK	Internal AHB clock frequency			0	72	ure)	
	fPCLK1	Internal APB1 clock frequency			0	36	MHz	
	fPCLK2	Internal APB2 clock frequency			0	72		
	VDD	Standard Operating Voltage			2	3.6		
	V _{BbA}	Analog section operating voltage (without ADC)	mus as V same	- / ·	2	3.6	V	
		Analog section operating voltage (using ADC)	~		2.4	3.6		
	VBAT	Backup section operating voltage	分		1.8	3.6		
				Standard I/O	-0.3	VDD+0.3		
	VIN	I/O Input Voltage	FT I/O	2V <vdd<3.6v< td=""><td>-0.3</td><td>5.5</td><td></td><td></td></vdd<3.6v<>	-0.3	5.5		
				VDD=2V	-0.3	5.2		
		O'		BOOT0	0	5.5		
			I	LQFP100		434		
	PD	power dissipation		LQFP64		444		
	10	Temperature scale 6: T = 85°C		LQFP48		363	mW	
1 3371		Temperature scale 7: T = 105°C		QFN36		1000		
	_	ADC, see Table 43.	od to may		wp. tollow		OmV dif	foronco
be	tween _{voo} ar	nded that the same power supply № us Ambient temperature Id vdda during power-up and normal o	pera ti jog	sipation	vdda ,24UIOW	ing uggsto 30	om v an	referice
3. If t	he TA is lower	(temperature scale 6) higher povalues are allowed as long a	is the ∄d	ovesprontvexceed ™	max (S AO SeC	ion 1105		
4. In	states with l	ower power dissipation, TA can be ext	ended d ig	s shipatang eas lon	g as 11 does	not exceed	°C I _{TJmax} (se	e Section
1).		Ambient temperature	dis	aximum power ssipation	-40	105		
5.3.	2 Opeı	rating conditions at pov			er- d ow	n 125		
	-			ssipation ⁽⁴⁾				
7	The param	eters given in the following table Junction temperature range	were te	este de mather eger cale 6	iera#0per	atin g5 con	ditions	
		S32F103xB, a series of 32-bit MCUs from nufacturing Corp.		emperature cale 7	-40	125		38



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Table 7 Operating conditions at power-up and power-down

notati	parameters	conditional	minimum	maximu	unit (of
on			value	m values	measu
					re)
tVDD	_{VDD} Rise Rate		0	∞	ug/V
***==	_{VDD} Rate of		20	∞	μs/V
	Descent				

Embedded reset and power control module features 5.3.3

The parameters given in the following table are based on tests at ambient temperature and VDD supply voltage as listed in Table 6.

Table 8 Embedded Reset and Power Control Module Characteristics notation parameters prerequisite minimu typical maximu unit (of m value value m values measu re) PLS[2:0]=000 (rising edge) 2.10 2.18 2.26 V 2.00 2.07 2.16 V PLS[2:0]=000 (falling edge) 2.19 PLS[2:0]=001 (rising edge) 2.28 2.37 V 2.09 2.27 V PLS[2:0]=001 (falling edge) 2.17 PLS[2:0]=010 (rising edge) 2.28 2.38 2.48 V V PLS[2:0]=010 (falling edge) 2.18 2.27 2.38 PLS[2:0]=011 (rising edge) 2.38 2.47 2.58 V Programma VPVD PLS[2:0]=011 (falling edge) 2.28 V ble Voltage 2.37 2.48 Detector 2.47 V PLS[2:0]=100 (rising edge) 2.57 2.69 level PLS[2:0]=100 (falling edge) 2.37 2.46 2.59 V selection 2.57 2.79 V PLS[2:0]= 101 (rising edge) 2.67 2.47 2.56 2.69 V PLS[2:0]=101 (falling edge) PLS[2:0]= 110 (rising edge) 2.66 2.77 2.90 V PLS[2:0]=110 (falling edge) 2.56 2.66 2.80 V V PLS[2:0]=111 (rising edge) 2.76 2.86 3.00 2.66 2.76 2.90 V PLS[2:0]=111 (falling edge) VPVDhyst (2) 100 **PVD** hysteresis mV The characteristics of the product are guiling teetley design to a minimus on value of 850 RPP. V 1.96 Guaranteed by design partiested in producting (of a mountain 1.84 1.92 2.0 V range) reset Built-in reference voltage 5.3.4 value CKS32F103x8 and CKS32F103xB, a series of 32-bit MCUs from VPVDhyst 40 mV TRSTTEMPO $^{(2)}$ 1 2.5 4.5 Reset Duration





Datasheet parameters given in the following table are based on tests at ambient temperature and v_{DD} supply voltage as listed in Table 6.



Table 9 Built-in reference voltage

notatio	parameters	prerequisite	minimu	typical	maximu	unit
n			m value	value	m values	(of
						measu
						re)
VREFINT	Built-in reference	$-40^{\circ}\text{C} < \text{TA} < +105^{\circ}\text{C}$	1.16	1.20	1.26	V
	voltage	-40°C < TA< +85°C	1.16	1.20	1.24	V
TS_vref (1)	When the internal reference voltage is			5.1	17.1 ⁽²⁾	μs
	read					
	ADC Sampling Time					

- 1. The characteristics of the product are guaranteed by design to a minimum value of VPOR/PDR.
- 2. Guaranteed by design, not tested in production.

5.3.5 Supply Current Characteristics

Current consumption is a combination of a number of parameters and factors including operating voltage, ambient temperature, load on I/O pins, software configuration of the product, operating frequency, flip-flop rate of I/O pins, location of the program in memory, and code executed.

See Figure 11 for a description of how current consumption is measured.

All of the current consumption measurements given in this section for the operating modes are obtained by executing a streamlined set of codes that are able to

Dhrystone2.1 code equivalent results.

Maximum current consumption

The microcontroller is in the following conditions:

- All I/O pins are in input mode and connected to a static level VDD or VSS (no load).
- All peripherals are off unless otherwise noted.
- The flash memory access time is adjusted to the frequency of fHCLK (0 wait cycle for 0~24MHz, 1 wait cycle for 24~48MHz, and 2 wait cycles for more than 48MHz).
- Command prefetch is turned on (hint: this parameter must be set before setting the clock and bus divider).
- When the peripheral is turned on: fPCLK1 = fHCLK/2, fPCLK2 = fHCLK.

The parameters given in Tables 10, 11, and 12 are based on tests at the ambient temperatures and VDD supply voltages listed in Table 5.

Table 10 Maximum Current Consumption in Run Mode with Data Processing Code Running from Internal

CKS32F103x Semicondu	notati 8 and cks3 on ictor Manu	1	Fla prerequisite f32-bit MCUs from		Maximur TA= 85°C	n value ⁽¹⁾ TA= 105°C	unit (of meas ure)	41
				72MHz	50	50.2		

Datasheet



	36MHz	19.8	19.9	
	24MHz	13.9	14.2	
	16MHz	10.7	11	
	8MHz	6.8	7.1	

- 1. Derived from a comprehensive assessment and not tested in production.
- 2. External clock is 8MHz, PLL is enabled when fHCLK>8MHz.

Table 11 Maximum Current Consumption in Run Mode with Data Processing Code Running from Internal

notati on	paramet ers	prerequisite	RAM	Maximui TA= 85°C	m value ⁽¹⁾ TA= 105°C	unit (of
						meas ure)
			72MHz	48	50	
			48MHz	31.5	32	
		External	36MHz	24	25.5	
		clock ⁽²⁾ tomble	24MHz	17.5	18	
	0 1	all	16MHz	12.5	13	
IDD	Supply	peripherals	8MHz	7.5	8	mA
	current in operating	113	72MHz	29	29.5	
	mode		48MHz	20.5	21	
	111040	External	36MHz	16	16.5	
		alaala?tturra	I			

1. Derived from a comprehensive evaluation and tested 24 Metauction with 5 VDD max and 2 HCLK max as conditions.

2. External clock is 8MHz, PLL is enabled when fHCLK 8MH6MHz 8.5 9 peripherals 8MHz 5.5 6

Table 12 Maximum current consumption in sleep mode with code running in Flash or RAM

	notati on	paramet ers	conditional	fHCLK	Maximur TA= 85°C	n value (1) TA= 105°C	unit (of
							meas
							ure)
				72MHz	30	32	
				48MHz	20	20.5	
			External	36MHz	15.5	16	
		Supply	clock ⁽²⁾ to	24MHz	11.5	12	
	IDD	current in	enable all	16MHz	8.5	9	mA
		sleep	peripherals	8MHz	5.5	6	
		mode	External -	72MHz	7.5	8	
				48MHz	6	6.5	
CKS32F103x	and cks3 : ctor Manu	2F103xB, a series o facturing Corp.	clock ⁽²⁾ to f32-bit MCUs from turn off all	36MHz	5	5.5	
			peripherals				



24MHz	4.5	5
16MHz	4	4.5
8MHz	3	4

- 1. Derived from a comprehensive evaluation, tested in production with VDDmax and with fHCLKmax enabling the peripheral as a condition.
- 2. External clock is 8MHz, PLL is enabled when fHCLK>8MHz.

Table 13 Typical and Maximum Current Consumption in Stop and Standby Modes

	<i>J</i> 1			1			
			typical	value	ma	ximum	
notati	paramet	prerequisite			val	ues	unit
on	ers		VDD/VBAT	VDD/VBAT	TA=	TA=	(of
			= 2.4V	= 3.3V	85°C	105°C	meas
							ure)
		Regulator is in run mode, low and					urc)
		high speeds	22.7	23.4	200	370	
	Supply	Internal RC oscillator and	22.1	23.4	200	3/0	
	current in	high-speed oscillator off (no					
	shutdown	independent watchdog)					
	mode	The regulator is in low-power					
IDD	inode	mode with low and high	9.1	10.3	180	340	
		The internal RC oscillator	9.1	10.5	100	340	
		and high-speed oscillator are	XX				μА
		off (no independent	ZXX				
		watchdog).					
		Low-speed internal RC					
		oscillator and independent	2.4	2.06	-	-	
		watchdog					
	Supply	in the on state					
	current in	1					
	standby	Low-speed internal RC oscillator on	2.3	2.81	-	-	
	mode						
		state, independent watchdog is					
		in off state					
		Low-speed internal RC	_				
		oscillator and independent	1.5	3.17	4	5	
		watchdog					
		is off, the low-speed oscillator and					
		RTC					
		stalled					

CKS32F103	3x8 and CKS32F10	3xB		CEIC		果似电路行	
Da te b <u>l</u> vet	The backup	Low-speed oscillator and RTC	11	14	1 9(2)	2.2	
AT	area of the	1	1.1	1.4	1.5	2.2	
	Supply	on					
	current						

- 内科女生成中的方明八字

- 1. Typical values are tested at TA=25°C.
- 2. Derived from a comprehensive assessment and not tested in production.

Typical Current Consumption

The MCU is under the following conditions:

- All I/O pins are in input mode and connected to a static level VDD or VSS (no load).
- All peripherals are off unless otherwise noted.
- The flash memory access time is adjusted to the frequency of fHCLK (0 wait cycle for 0~24MHz, 1 wait cycle for 24~48MHz, and 2 wait cycles for more than 48MHz).
- Ambient temperature and VDD supply voltage conditions are listed in Table 6.
- Command prefetch is turned on (hint: this parameter must be set before setting the clock and bus divider). When the peripheral is turned on:
 - fPCLK1= fHCLK/4, fPCLK2= fHCLK/2, and fADCCLK = fPCLK2/4.



Table 14 Typical Current Consumption in Run Mode with Data Processing Code Running from Internal Flash

	notat	paramet ers	prereq uisite	fHCLK	Typical Enable all peripherals ⁽²⁾	value ⁽¹⁾ Turn off all peripherals	unit (of meas ure)	
		C		72MHz	32.46	21.7		
1. Typical	values a	re tested at TA=	2 EX te¥DD	=3. 4 8MHz	21.96 to the APC ₁ for each	14.73	mΛ	
2. An add	tional 0.	8mA of current	comsulmpt	ion is added	to the APC ₁ f3r each	analog sec t ion. In	the applic	ation
enviro	hment, t	his current is o Mode	nlyd l ggrea	sed when the	ADC is turned on (se	tting the ADON bi	t of the AI	DC_CR2
registe	r).		ks ⁽³⁾					

^{3.} External clock is 8MHz, PLL is enabled when fHCLK>8MHz.

Table 15 Typical Current Consumption in Run Mode with Data Processing Code Running from Internal RAM

	notat	paramet	prereg	fHCLK	Typical	value ⁽¹⁾	unit	
	ion	1	uisite		Enable all	Turn off all	(of	
	1011	ers	uisite		peripherals ⁽²⁾	peripherals	,	
							meas	
							ure)	
		Sunnly		72MHz	24.84	14.21		
1. Typical	values a	Supply re tested at TA=	2 EX te¥DD	=3. 48 MHz	17.17	10.05	mΛ	
2. An addi	tional 0	8mA of current	comsulmpt	ionziemelded	to the ADG for each	analog şestion. In	the applic	ation
enviro	hment, t	his current is o	nlyc ilo crea	sed when the	ADC is turned on (see	tting the ADON bi	of the AI	DC_CR2
registe	r).	1,10 40	ks ⁽³⁾					

^{3.} External clock is 8MHz, PLL is enabled when fHCLK>8MHz.

Table 16 Typical Current Consumption in Sleep Mode with Data Processing Code Running from Internal

Flash or RAM

notation	parameters	prere quisit e	fHCLK	Typical Enable all peripherals ⁽²⁾	value ⁽¹⁾ Turn off all peripherals	unit (of meas ure)
IDD	Supply currentin sleep mode	Exter nal cloc ks ⁽³⁾	72MHz	17.57	17.61	mA

^{1.} Typical values are tested at TA=25°C, VDD=3.3V.

^{2.} An additional 0.8mA of current consumption is added to the ADC for each analog section. In the application environment, this current is only increased when the ADC is turned on (setting the ADON bit of the ADC CR2



3. External clock is 8MHz, PLL is enabled when fHCLK>8MHz.

Built-in peripheral current consumption

The current consumption of the built-in peripherals is listed in Table 17, and the operating conditions of the MCU are as follows:

• All I/O pins are in input mode and connected to a static level - VDD or VSS (no load).



- All peripherals are off unless otherwise noted.
- The values given are calculated by measuring current consumption
 - Turn off the clock for all peripherals
 - Turn on the clock for only one peripheral
- \bullet Ambient temperature and $_{V\!D\!D}\!$ supply voltage conditions are listed in Table 4.

Table 17 Current consumption of built-in peripherals⁽¹⁾

		lt-in	Typical power	unit	bı	uilt-in	Typical work at 25°C	unit
	per	ripherals	consumption at 25°C	(of	ре	eripherals	dilly-dally	(of
				meas				meas
				ure)				ure)
		TIM2	1.2			GPIOA	0.47	
		TIM3	1.2			GPIOB	0.47	
		TIM4	0.9			GPIOC	0.47	
		SPI2	0.2			GPIOD	0.47	
	APB1	USART2	0.35	mA	APB2	GPIOE	0.47	mA
		USART3	0.35		7 (ADC1 ⁽²⁾	1.81	
		I2C1	0.39	, X	1	ADC2	1.78	
1. гнс	$c_{LK} = 72M$	Hz, <u>I2C2</u> Hz, _{fapb1} = fHC	0.39 CLK/2, fAPB2 = fHCLK, and the	prescal	er coeffic	TIM1 cients for each	peripheral are default	values.
2. Sp	ecial co	nditions for A	0.65 ADC: fhclk = 56MHz, fapb1 =	fHCLK/2	$\int_{fAPB2} = fH$	SPI1 CLK, fADCCLK = fA	0.43 APB2/4, and ADON=1 in	ADC_CR
re	gister.	CAN	0.72	*		USART1	0.85	

5.3.6 External Clock Source Characteristics

High-speed external user clock generated from an external oscillator source

The characterization parameters given in the following table were measured using a high-speed external clock source with ambient temperature and supply voltage in accordance with the conditions in Table 6.

Table 18 High-Speed External User Clock Characteristics

		Table 18 High-Speed Exte	ernar Oser Cro	K Gharac	teristics		
	notation	parameters	prerequisite	minimu	typical	maximu	unit
				m value	value	m	(of
						values	measu
							re)
	fHSE_ext	User External Clock		1	8	25	MHz
		Frequency ⁽¹⁾					
	VHSEH	OSC_IN Input pin high voltage		2.2		3.3	v
	VHSEL	OSC_IN Input pin low level		0		2.2	·
CKS	2F103x8 and C	KS32F103xB, a series of 32-bit MCUs from					
Sem	tw (HSE)	anufacturing Corp.					
	tw (HSE)	OSC_IN High or low time ⁽¹⁾		5			
	tr(HSE)						ns
		OCC IN Time of rice or foll(1)				20	



Data	sheet						
	DuCy (HSE)	duty cycle		45	50	55	%
	IL	OSC_IN Input leakage current	VSS≤VIN≤VDD		0.3	±1	μΑ

^{1.} Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external oscillator source

The characterization parameters given in the following table were measured using a low-speed external clock source with ambient temperature and supply voltage in accordance with the conditions in Table 6.

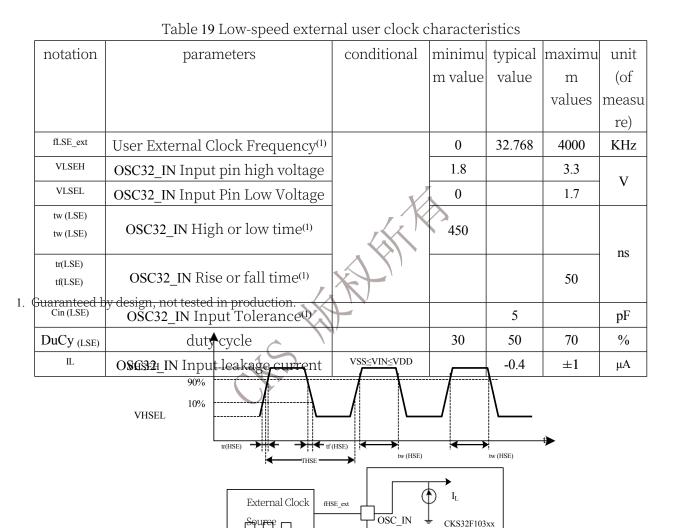


Fig. 12 AC Timing Diagram of External High-Speed Clock Source



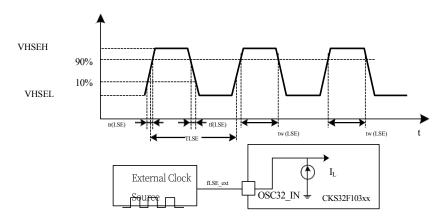


Figure 13 AC Timing Diagram for External Low Speed Clock Source

High-speed external clock generated using a crystal/ceramic resonator

The High Speed External Clock (HSE) can be generated using an oscillator consisting of a 4 to 16 MHz crystal/ceramic resonator. The information given in this section is based on a comprehensive characterization using typical external components listed in the table below. In the application, the resonator and load capacitance must be placed as close as possible to the oscillator pins to minimize output distortion and stabilization time at startup.

Table 20 HSE 4~16MHz	Oscillator	· Characteristics ⁽¹⁾⁽²⁾

	notation	parameters	prerequisite	minimu	typical	maximu	unit (of	l
			(C)	m value	value	m values	measure	l
)	
	fOSC_IN	oscillator frequency) >	4	8	16	MHz	
	RF	Feedback resistance			200		kΩ	
	CL1	Recommended load	D 200		20		F	
	CL2 ⁽³⁾	capacitance with	$Rs=30\Omega$		30		pF	
		corresponding						
		The crystal serial						
1.	Resonator c	impedance (RS) of the naracterization parameters a	re given by the crystal/cer	amic reson	ator manu	facturer.		
2.	Derived from	n a comprehensive assessme	nt and not tested in produ	ction.				
3	For Ga and	curitistrecommended to	Use high quality cerami	l Ic dielectric	capacito	rs between	5pE and 2	5r

- 3. For cm and cl2, His is Defrommended to use high quality versamic dielectric capacitors between 5pFmand 25pF (typical) designed for high frequency applicately a
- 4. Relatively low RF resistance values can provide protection against problems associated with use in humid environments where leakage and bias conditions change. However, this parameter needs to be taken into account when designing MCUs for use in harsh, humid conditions.

CKS32F103x8 and CKS32F103xB



Betasheet is the startup time, which is the period of time from when the software enables HSE until a stable 8MHz oscillation is obtained. This value is measured on a standard crystal resonator and may vary greatly depending on the crystal manufacturer.



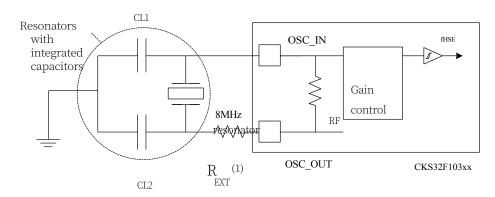


Figure 14 Typical Application Using 8MHz Crystals

1. The $_{REXT}$ value is determined by the characteristics of the crystal. Typical values are 5 to 6 times $_{RS}$.

Low-speed external clock generated using a crystal/ceramic resonator

The Low Speed External (LSE) clock can be generated using an oscillator consisting of a 32.768kHz crystal/ceramic resonator. The information given in this section is based on a comprehensive characterization using typical external components listed in Table 21. In the application, the resonator and load capacitance must be placed as close as possible to the oscillator pins to minimize output distortion and stabilization time at startup.

Note: For $_{CLI}$ and $_{CL2}$, it is recommended to use high quality ceramic dielectric capacitors between 5pF and 15pF, and select a crystal or resonator that meets the requirements. Usually $_{CLI}$ and $_{CL2}$ have the same parameters. Crystal manufacturers usually give the load capacitance parameters as a serial combination of $_{CLI}$ and $_{CL2}$.

The load capacitance $_{CL}$ is calculated by the following formula: $_{CL} = _{CL1}x$ $_{CL2}/(_{CL1} + _{CL2}) + _{Cstray}$, where $_{Cstray}$ is the capacitance of the pins and the capacitance associated with the PCB board or PCB, and its typical value is $_{DCB}$ between $_{DCB}$ and $_{DCB}$.

WARNING: To avoid exceeding the maximum values of $_{CL1}$ and $_{CL2}$ (15pF), it is strongly recommended to use a resonator with a load capacitance $_{CL} \leq 7pF$, and not one with a load capacitance of 12.5pF.

For example, if a resonator with load capacitance CL=6pF and Cstray=2pF is selected, then CL1=CL2=8pF.

	Table 21 LSE OSCIII	ator characteristics	(ILSE=32.	/00K11Z) (
notation	parameters	prerequisite	minimu	typical	maximu	unit
			m value	value	m	(of
					values	measu
						re)
RF	Feedback resistance			5		ΜΩ
CL1	Recommended load	DS- 201 ₂ O			15	nE
CL2 ⁽²⁾	capacitance with	$RS=30k\Omega$			15	pF
	corresponding					

Table 21 LSE oscillator characteristics (fLSE=32.768kHz) (1)

1 100A0 ana 0.	110021 10011				CHINA KEY SYSTEM & IN	TEGRATED CIRCUIT CO.
eet	The crystal serial					
	impedance (RS) of the					
	(3)					
I2	LSE Drive Current	VDD=3.3V, VIN=VSS			1.4	μА
gm	Transconductance of		5			μA/V
	the oscillator					
tSU(LSE) ⁽⁴⁾	activation time	_{VDD} stabilization		3		s
ī	12 gm	impedance (RS) of the (3) LSE Drive Current Transconductance of the oscillator	The crystal serial impedance (RS) of the (3) LSE Drive Current VDD=3.3V, VIN=VSS Transconductance of the oscillator	The crystal serial impedance (RS) of the (3) LSE Drive Current VDD=3.3V, VIN=VSS Transconductance of the oscillator The crystal serial impedance (RS) of the oscillator	The crystal serial impedance (RS) of the (3) LSE Drive Current VDD=3.3V, VIN=VSS Transconductance of the oscillator The crystal serial impedance (RS) of the crystal serial impedance (RS) of the crystal serial impedance (S) of the crystal serial impedance (S) of the crystal serial impedance (RS) of the c	The crystal serial impedance (RS) of the (3) LSE Drive Current VDD=3.3V, VIN=VSS Transconductance of the oscillator The crystal serial impedance (RS) of the crystal serial impedance (RS) of the crystal serial impedance (S) of the crystal serial impedance (S) of the crystal serial impedance (RS) of the c

- 1. Derived from a comprehensive assessment and not tested in production.
- 2. See the Notes and Warnings paragraph at the top of this form.
- 3. Current consumption can be optimized by choosing a high quality oscillator with a small $_{RS}$ value (e.g. MSIV-TIN32.768kHz).
- 4. _{ISU(HSE)} is the startup time, measured from the time the software enables HSE until a stable 8MHz oscillation is obtained. This value is measured on a standard crystal resonator and may vary greatly depending on the crystal manufacturer.



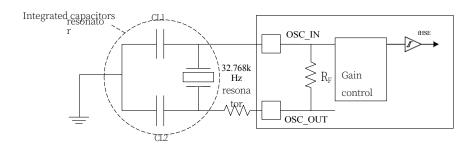


Figure 15 Typical Application Using 32.768kH Crystals

5.3.7 Internal Clock Source Characteristics

The characteristics given in the following table were measured using ambient temperatures and supply voltages in accordance with Table 6.

High Speed Internal

(HSD RC Oscillator

Table 22 HSI Oscillator Characteristics⁽¹⁾⁽²⁾

(1151) 1	C OSCIII	201		-///			
	notation	parameters	conditional	minimu	typical	maximu	unit
			. 🛇	m value	value	m values	(of
				۱ ۱			measu
							re)
	fHSI	frequency			8		MHz
			TA= -40~105°C	-2		2.5	%
	ACCHSI	HSI Oscillator	TA= -10~85°C	-1.5		2.2	%
		Accuracy	TA= 0~70°C	-1.3		2	%
1. vpp = 3.3	3V TA=-40	to 105°C, unless otherwise	TA= 25°C	-1.1		1.8	%
2. Guarai	tSU (HSI) nteed by des	HSI Oscillator Startup sign, not tested in product	ion.	1		2	μs
		Time					
Low St	IDD (HSI) peed Into	HSI Oscillator Power			80	100	μΑ
		Consumption T	able 23LSI Oscill	ator Cha	acterist	CS ⁽¹⁾	

(LSI) RC Oscillator

	notation	parameters	minimu	typical	maximu	unit (of
			m value	value	m	measu
					values	re)
	fLSI (2)	frequency	30	40	60	kHz
		less Just Oscillated.			85	μs
2. Derived from a c	omprehensiv	Startup Time e assessment and not test	ed in prod	uction.		
3. Guaranteed by d	JDD(LSI) esign, not tes	LSI Oscillator Power and in production.		0.65	1.2	μА
•		Consumption				

Wake-up time from low-power mode



The wake-up times listed in Table 24 were measured during the wake-up phase of an 8MHz HSI RC oscillator. The clock source used for wake-up depends on the current operating mode:

- Stop or standby mode: clock source is an RC oscillator
- Sleep mode: the clock source is the clock used when entering sleep mode

All times were measured using ambient temperatures and supply voltages in accordance with Table 6.

Table 24 Wake-up times for low-power modes

					Table 24 Wake-	up	times for I	ow-power	modes			
		notati	on		parameters		pr	erequisite		typical	unit	
								_		value	(of	
											meas	
											ure)	
		tWUSLEE	(1)	Wak	te from sleep		Wake-up	with HSI R	C Clock	1.7	,	
				mod	le							
				Wal	ke-up from		uci pc ol	ock wakeı	ın – 2	2.6		
1.	Wa	keWipTOF	ne is	shu measi (vol	tdown mode ured from the start of tage regulation)	the	e wake-up ev	ent until the	ıp — 2µs e user progra ı	m reads t	μs he first i	nstruction.
5.3	5.3.8 PLL Characterizat			device is in run		~						
	Th	e paran	nete	rs list	ke-up from ted in Table 25 wer tdown mode	e r	HSI RC cl neasured u Regulator v	ock wakeu Ising ambi Wake-up ti	ıp = 2μs ent tempe me from	ratures a	nd sup	ply voltages
	in a	ccorda	nce	withı	Tableregulation)		(A)	wer mode				
				The	device is in Table	251	PLL Charac	teristics				
			n	Weg	er mode) meters)	nu	merical va	lue	unit		
		+W/I ISTIND			te up from			odkrivate	1	(off2		
		twosibb	1 0.		dby mode	Re	gu latoe wa	1 *	enfrontuess			
				Starr	aby mode		m	$ode = 38\mu s$		meas		
										ure)		
					PLL Input Clock	(2)	1	8.0	25	MHz		
				L_IN	PLL Input Clocl		40	50	60	%		
1. I)eriv	ed from a	a con	nprehe	ensive Datysfiyot and	d no	t tested in pr	oduction.		, •		
2. (Care	needs to	be ta	ıken to	us eptuticleresed dia	øe f	actor so that	fPLL_OUT IS WI	thin the allo	wable ran	ge based	on the PLL
i	nput	clock fre	eque:	ncy.	comparison and "-	er						
					than")							
5.3	.9	Stor	age	e Ch	aracteristics		16		72	MHz		
					Output Clock							
fla	sh :	memo	ry tL	OCK	PLL phase-lock tii	ne		43	200	μs		
			-									

Unless otherwise noted, all characteristics are obtained at TA=-40~105°C.



Table 26 Flash memory characteristics

		bic 20 i iasii ilicilioi y ciiai					
notatio	parameters	conditional	minii	mu typ	ical	maximu	unit
n			m val	lue va	lue	m	(of
						values	measu
							re)
tprog	16-bit programming	TA= -40~105°C	-		-	20	μѕ
	time						
tERASE	Page (1K bytes) Erase	TA= -40~105°C	-			2	
	Time						ms
tME	Whole chip erase	TA= -40~105°C	-			10	
1. Guaran	teed by des ign enot						
tested in pro		ab k-27 dFlashememory life					
n	tati parameters	fHCLK=72MHz, 2 wait	minimu	typical	ma	xim21.6un	
IDD	on Supply Current	1	m value	value	um	(o	f mA
		Write/erase mode.			val	ues mea	lsu
		fHCLK=72MHz, VDD=3.3	V			3 re	
1. Derived N	from a comprehensive ass	essmentand colfested in pro	duction.			ithou	ISA _{LI} A
		Standby mode, $A = -40$ to 105 °C (with a 7 VDD=3.3~3.6V				l l no	[] [
5.3.10	EMC Characteri						
						tim	
Sensiti	vity testing is performe period	TA = 40-85°C ed on a sample of products	s during a	a comp	ehe:	nsive eva m	na lluation of e
produ	ct.	115				Nia	an

Functionality EMS (Electromagnetic Sensitivity)

When running a simple application (2 LEDs blinking through the I/O port), the test sample is subjected to 2 types of electromagnetic interference until an error is generated, which is indicated by the blinking of the LEDs.

- **Electrostatic discharge (ESD)** (positive and negative discharge) is applied to all pins of the chip until a functional error is generated. This test complies with the IEC61000-4-2 standard.
- **FTB:** A pulse train of transient voltages (forward and reverse) is applied across _{VDD} and _{VSS} through a 100pF capacitor until a functional error is generated. This test complies with the IEC61000-4-4 standard.

A chip reset restores the system to normal operation. The test results are listed in the table below.

		Table 28 EMS (Characteristics		_
	notatio n	parameters	prerequisite	Level/class model	
CKS Ser	VFESD 32F103x8 a niconduct	applied to any I/O pin, which results in and CKS32F103xB, a series of 32-bit MCUs from a functionally incorrect cor Manufacturing Corp. Voltage Limits.	$_{ m VDD}$ = 3.3V, $_{ m TA}$ = +25 °C. $_{ m fHCLK}$ = 72MHz. in accordance with IEC61000-4-2.	2В	55
	VEFTB	Transient pulse group voltage limits on vDD and vSS applied through a 100pF	$_{\rm VDD}$ = 3.3V, $_{\rm TA}$ = +25 °C. $_{\rm fHCLK}$ = 72MHz. in accordance with	4A	



Designing robust software to avoid noise problems

Evaluation and optimization of EMC at the device level is performed in a typical application environment. It should be noted that good EMC performance is closely related to the user application and specific software.

Therefore, it is recommended that the user optimizes the software for EMC and performs EMC-related certification tests.

Software Recommendations

The flow of the software must include controls for the program to run and fly, for example:

- Destroyed program counters
- Unexpected reset
- Critical data destroyed (control registers, etc.)

Pre-certification tests

Many common failures (accidental resets and corrupted program counters) can be reproduced by artificially introducing a low level on NRST or a low level on the crystal pins that lasts 1 second.

During ESD testing, voltages in excess of the application requirements can be applied directly to the chip, and where unexpected actions are detected, the software section needs to be enhanced to prevent unrecoverable errors.

Electromagnetic interference (EMI)

The EMF emitted by the chip is monitored while running a simple application (blinking 2 LEDs through the I/O port). This emission test complies with SAE J1752/3, which specifies the loads on the test board and pins.

Table 29 EMI Characteristics

notat ion	para mete	prerequisite	Frequency bands	(fHSE/fHCLI	Maximum (fHSE/fHCLK) 8/48MHz 8/72MHz	
	rs		monitored	0, 101,112	077211111	meas
						ure)
			0.1~30MHz	12	12	
		VDD= 3.3 V, TA=	30~130MHz	22	19	dBμV
SEMI	peak		130MHz~1GHz	23	29	
	value	package according	SAM EMI Class	4	4	_
		to IEC 61967-2	pin	7	T	

5.3.11 Absolute maximum (electrical sensitivity)



Datash Based on three different tests (ESD, LU), using specific measurements, the chip is strength tested to determine its performance in terms of electrical sensitivity.

Electrostatic Discharge (ESD)

An electrostatic discharge (a positive pulse followed by a negative pulse one second later) is applied to all pins of all samples, the size of which is related to the number of power supply pins on the chip (3 slices x (n+1) power supply pins). This test complies with the JESD22-A114/C101 standard.



Table 30 ESD Absolute Maximum Values

		notation	parameters	prerequisite	typolo	Maximum	unit	
					gy	value (1)	(of	
							meas	
							ure)	
1.		VESD (HBM) ed from a co	Electrostatic discharge mprehensive assessment and not voltage (human model)	T=+25°C, tester indireduction Hop JESD22- A114	. 2	2000	V	
	•	For each p	ting performance, 2 complements ower supply pin, discharge supply	pply yoltage that e	g tests xceeds	on 6 sampl the 1990 it.	es are 1	required:
	•	Current is	inglaged charging aquipment	it, and Hon IESD22-				

configurable I/O pin. This the the mplies with the C101 EIA/JESD 78A integrated circuit latch standard.

Table 31 Electrical sensitivity

		1 4510	51 Electrical scriptcivity	
	notati	parameters	prerequisite	typolog
	on			У
	LU	Static bolts	T = +105 °C according to	Categor
I/O Port	Cha	racteristic	S JESD78A	y II A

Generalized Input/Output Characteristics

Unless otherwise noted, the parameters listed in the following table were measured according to the conditions in Table 6. All I/O ports are CMOS-compatible and

TTL.

5.3.12

Table 32 I/O Static Characteristics

		1 able 3	2 I/O Static Characteristi	.CS		1
notati	parameters	prerequisite	minimum value	typical	maximum values	unit
on				value		(of
						measu
						re)
		Standard I/O Pin,			0.28×(VDD-2V)+0.8V	
	VII. Low Level Input Voltage	Input	-	_	0.28^(VDD-2V)+0.8V	
VIL		Low Level				
		Voltage				
		FT I/O ⁽¹⁾ pin,			0.32 x (VDD-2V)	
		input			+0.75V	v
		Low Level				,
		Voltage				
		All I/O ports			0.25	_
		except			$0.35_{ m VDD}$	
0.00	32F103x8 and CKS32F103xB	-	- f			F0
Sen	32F103x8 and CKS32F103xB niconductor Manufacturin	, a series of 32-bit MCU g Standard I/O Pin,				- 58
		Input	0.41×(VDD-2V)+1.3V			
VIH	High Level Input	High Level				
VIII	riigii Levei iiiput	Voltage				



L	asheet				1	
	Trigger voltage					
	hysteresis ⁽²⁾					
	5V Tolerant to I/O					
	Pin Schmitt		5%VDD ⁽³⁾			
	Trigger Voltage					
	Hysteresis					
	(2)					
		$VSS \le VIN \le VDD$			±1	
Ilkg	Input Leakage	Standard I/O			-1	μА
	Current ⁽⁴⁾	Ports				μ. ι
	Guitent	$_{VIN} = 5V$.			3	
		5V Tolerance			3	
		Port				
RPU	Weak pull-up	$_{ m VIN} = _{ m VSS}$	30	44	50	1.0
	equivalent					kΩ
	resistance ⁽⁵⁾					
RPD	Weak pull-down	$_{ m VIN} = _{ m VDD}$	30	44	50	
	equivalent					
	resistance ⁽⁵⁾					
CIO	I/O Pin			5		pF
	Capacitance					

- 1. FT = 5V Tolerance.
- 2. Hysteresis voltage of the Schmitt trigger switching level. Derived from a comprehensive evaluation and not tested in production.
- 3. The voltage is at least 100mV.
- 4. The leakage current may be higher than the maximum value if there is a reverse current back-up at an adjacent pin.
- 5. The pull-up and pull-down resistors are designed as a true resistor in series with a switchable PMOS/NMOS implementation. The resistance of this PMON/NMOS switch is very small (about 10%).

All I/O ports are CMOS- and TTL-compatible (no software configuration required), and their characteristics take into account most of the stringent CMOS process or

TTL parameters:

- For VIH:
 - If _{VDD} is between [2.00V~3.08V]; use CMOS characteristics but include TTL.
 - If VDD is between [3.08V~3.60V]; use TTL characteristics but include CMOS.
- For VIL:
 - If vDD is between [2.00V~2.28V]; use TTL characteristics but include CMOS.
 - If vDD is between [2.28V~3.60V]; use CMOS characteristics but include TTL.

Output drive current

The GPIOs (General Purpose Input/Output Ports) can absorb or output up to +/-8mA and



Datashab sorb +20mA (not strictly V). In user applications, the number of I/O pins must be such that the drive current does not exceed the absolute maximum ratings given in section 5.2:

- The sum of the currents drawn by all I/O ports from V, plus the maximum operating current drawn by the MCU on V, must not exceed the absolute maximum rating, IVDD (see Table 4).
- The sum of the currents absorbed by all I/O ports and flowing off of V, plus the maximum operating current flowing off of V by the MCU, must not exceed the absolute maximum rating of IVSS (see Table 4).

output voltage

Unless otherwise noted, the parameters listed in Table 33 were measured using ambient temperatures and $_{\rm VDD}$ supply voltages in accordance with Table 6. All The I/O ports are CMOS and TTL compatible.



Table 33 Output Voltage Characteristics

notati	parameters	prerequisite	minimu	maximu	unit
on			m value	m	(of
				values	meas
					ure)
VOL (1)	Output low, when all 8 pins draw	CMOS port, IIO=		0.4	
	current at the same time	+8mA			
Ven	Output high, when all 8 pins output	2.7V < VDD< 3.6V	VDD-0.4		
	current at the same time				v
VOL (1)	Output low, when all 8 pins draw	TLL Port, IIO = +8mA		0.4	·
1. The curre	ent 110 absorbed by the chip must always follow	w the 2absolute maximum ra	ings given	in Table 4	, while the
VOH SUM of the	Output high, when all 8 pins output	eed ivss.	2.4		´
The curre	current at the same time ent no output from the chip must always follo	w the absolute maximum ra	tings giver	in Table 4	whileth
VOL Sum of the	Output low, when all 8 pins draw all 1/0 pins and control pins) must not exc	$_{\rm IIO}$ = +20mA	111163 61 ()	1.3	, willie til
1 Dorivod f	current at the same time	2.7V < VDD < 3.6V			
VOH	current at the same time rom a comprehensive assessment and not teste Output high, when all 8 pins output	ed in production.	2.4		
 Input/Oเ	tput Ac Characteristics ime				
	efinitions and values of the input and o	output AC characteristic	s are give	0.4 n in Figu	re 16 and
Table	34, respectively.	2V < VDD< 2.7V		1	
vo _H Unles	Output high, when all 8 pins output s otherwise specified, the listed parame	ters were measured usir	VDD-0.4 ig ambier	ıt temper	atures a
supply	current at the same time voltages in accordance with Table 6.				

Table 34 Input/Output AC Characteristics⁽¹⁾

MODEx[1:0]	notation	parameters	prerequisite	minimu	maxim	unit
				m value	um	(of
					values	meas
						ure)
10	fmax(IO)out	Maximum frequency ⁽²⁾	CL= 50 pF,VDD= 2~3.6V		2	MHz
(2MHz)	tf(IO)out	Output high to low level fall time	CL= 50 pF,VDD= 2~3.6V		125(3)	ns
	tr(IO)out	Output low-to-high rise time			125(3)	
01	fmax(IO)out	Maximum frequency ⁽²⁾	CL= 50 pF,VDD= 2~3.6V		10	MHz
(10MHz)	tf(IO)out	Output high to low level fall time	CL= 50 pF,VDD= 2~3.6V		25(3)	ns
	tr(IO)out	Output low-to-high rise time			25(3)	
CKS32F103x8 and Semiconductor N		a series of 32-bit MCUs from Corp. Maximum	CL= 30 pF,VDD= 2.7~3.6V		50	61 MHz
		frequency ⁽²⁾	CL= 50 pF,VDD= 2.7~3.6V		30	1411.12
11			CL=50 pF,VDD= 2~2.7V		20	
1 11			01 00 DIVER		=(2)	

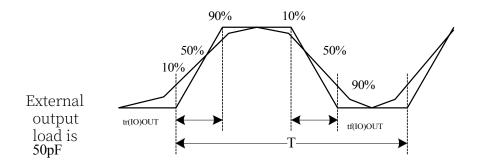




1. The speed of the I/O port can be configured via MODEx[1:0]. See the CKS32F103x8 and CKS32F103xB reference manuals for a description of the GPIO port configuration registers.

Pulse width of No.

- 2. The maximum frequency is defined in Figure 16.
- 3. Guaranteed by design, not tested in production.



If $(t_r + t_f) \le 2/3T$, and the duty cycle is (45-55%) Maximum frequency is reached when the load is 50pF

Fig. 16 Definition of Input and Output AC Characteristics

NRST Pin Characteristics 5.3.13

The NRST pin input driver uses a CMOS process which connects a pull-up resistor, RPU, that cannot be disconnected (see Table 32). Unless otherwise noted, the parameters listed in Table 35 were measured using ambient temperature and VDD supply voltage in accordance with Table 6.

parameters

Table 35NRST Pin Characteristics

conditio minimu typical maximu unit

		I			-J I			1
			nal	m value	value	m values	(of	
							measu	
							re)	
	VIL(NRST) ⁽¹⁾	NRST Input Low Level		-0.5		0.8	V	
		Voltage					V	
	VIH (NRST (1)	NRST Input High Voltage		2		VDD+0.5		
	(1)	NRST Schmitt Trigger			200		m V	
1. Guara	whys(NRST)(*) Inteed by desig	gn, not test of tage duction.			200		mV	
2. The p	ull-up resisto	r is designed shaggish resistor in se	eries with a	switchabl	e PMOS in	plementat	ion. The	resistance of
this P	MON/RPMOS sv	vitdWeakepudhub(equivalent	VIN=VSS	30	40	50	kΩ	
		resistance ⁽²⁾						
	VF (NRST) (1)	NRST Input Filter Pulse				100	ns	
CV\$22E10	(1) VNF (NRST)	NRST Input Unfiltered Pulse 03xB, a series of 32-bit MCUs from		300			ns	62
02								

notation



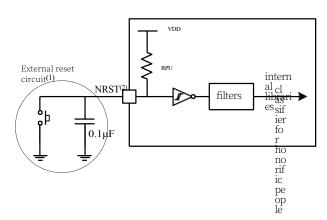


Figure 17 Recommended NRST Pin Protection

- 1. The reset network is designed to prevent parasitic resets.
- 2. The user must ensure that the potential of the NRST pin can fall below the maximum VIL(NRST) listed in Table 35, otherwise the MCU cannot be reset.

TIM Timer Features 5.3.14

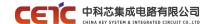
The parameters listed in Table 36 are guaranteed by design.

For details on the characteristics of the input/output multiplexing function pins (output compare, input capture, external clock, PWM output), refer to Section 5.3.12.

Sections.

Table 36TIMx ⁽¹⁾ Characteristics							
	notation	parameters	prerequisite	minimu maximum		unit (of	
				m value	values	measure	
)	
	tres(TIM)	Timer Resolution C	\	1		tTIMxCLK	
	ues(11.11)	Time Time	fΓIMxCLK= 72MHz	13.9		ns	
		· · ·			(TY) 1 (3) 17 (2)		
	fEXT	Timers for CH1 to		0	fTIMxCLK/2	MHz	
		CH4	$_{\rm fTIMxCLK} = 72 \rm MHz$	0	36	MHz	
		External Clock					
		Frequency					
1. TIM:	x is a generic i	naTimeraResoltstionTIM1	~TIM4.		16	bit	
	tCOUNTER	When the internal		1	65536	tTIMxCLK	
5.3.15		nunications inte	f face CLK= 72MHz	0.0139	910	μs	
		16-bit Counter Clock					
I2C In	terface Fe	atures					
Un	lessotherw	l ise noted, the paramet Maximum possible	ers listed in Table	50 and Ta	a167536x65536 ₁₁	tTIMxCLK neasured	

ambient temperature, iPCLK1 frequency, a fall with Table 6. The I2C interface of the CKS32F103x8 and CKS32F103xB standard models conforms to the standard I2C CKS32F103x8 and CKS32F103xB, a series of 32-bit MCUs from 63



 $\ensuremath{^{\text{Datasheet}}}$ communication protocol with the following limitations: SDA and

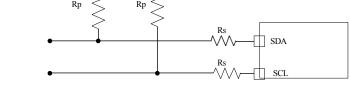
SCL is not a "true" open-drain pin; when configured as an open-drain output, the PMOS tube between the pin and $_{\mbox{\scriptsize VDD}}$ is turned off but still present.

The I² C interface characteristics are listed in Table 37 and see Section 5.3.12 for details on the characteristics of the input/output multiplexing function pins (SDA and SCL).



Table 37I² C Interface Characteristics

	notatio	parameters		Standard Fast I2C ⁽¹⁾		$C^{(1)(2)}$	unit	
	n		maximu	minimu	maximum	minimu	(of	
			m values	m value	values	m value	meas	
							ure)	
	tw(SCLL)	SCL Clock Low Time	4.7		1.3			
	twSCLH)	SCL Clock High Time	4.0		0.6		μs	
	tsu (SDA)	SDA build-up time	250		100			
	th (SDA)	SDA Data Hold Time	0(3)		0(4)	900(3)		
	tr(SDA) tr(SCL)	SDA and SCL Rise Time		1000	20+0. _{1Cb}	300	ns	
	tfSDA) tfSCL)	SDA and SCL downtime		300		300		
	th (STA)	Start condition hold time	4.0	- X	0.6			
	tsu (STA)	Repeat start condition	4.7		0.6		μs	
1. Guarai	teed by desi	establishment time gn, not tested in production.		(>),				
2. To ach	tsu (SŤO) ieve the max	Stop condition standard	4.0 l mode I² C,	fPCLK1 must	0.6 be greater th	an 2 MHz.	μs _{PCLK1} mu	st be greater
	MHz to achie		or fast mod	e I ² C.				
3. If an e	lo₩gææetsci	Timę from stop	1 1 1 1		hold ti3 ne fo	r the start o	on ds tio	h is required.
4. In orde	er to cross th	condition to start e undefined region of the falli condition	ng edge of S	CL, a holo	l time of at lea	ast 300ns or	the SD	A signal must
be gua	ranteed with	condition hin the MCU. Interval (Bus Idle)	VDD 12C					
	Cb	Tolerance load per bus	<u> </u>	400		400	pF	
$Rp \geqslant Rp \geqslant$								
		•		Rs .	SDA			



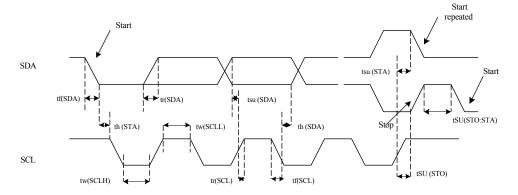


Figure 18 I2C Bus AC Waveform and Measurement Circuitry(1)

The measurement points are set at CMOS levels: 0.3 VDD and 0.7 VDD.



Table 38SCL frequency ($_{\text{PPCLK1}} = 36\text{MHz}$, $_{\text{VDD}} = 3.3\text{V}$) ($^{1)(2)}$

1 5				
fSCL(kHz)	I2C_CCR Values			
	RP=4.7 kΩ			
400	0x801E			
300	0x8028			
200	0x803C			
100	0x00B4			
50	0x0168			
20	0x0384			

- 1. RP= external pull-up resistor, fSCL=I² C speed.
- 2. For speeds around 200kHz, the error in speed is $\pm 5\%$. For other speed ranges, the error in speed is $\pm 2\%$. These variations depend on the accuracy of the external components in the design.

SPI Interface Features

ta(SO)

Data output access

Unless otherwise noted, the parameters listed in Table 39 were measured using the ambient temperature, fPCLKx frequency, and vDD supply voltage in accordance with the conditions in Table 6.

For details on the characteristics of the input/output multiplexing function pins (NSS, SCK, MOSI, MISO), see Section 5.3.12.

Table 39SPI Characteristics(1) conditional notation minimu maximu parameters unit m value m (of values | measu re) fSCK Master Mode 18 SPI Clock Frequency MHz 1/tc(SCK) 18 modal tr(SCK) SPI Clock Up and Load capacitance: C = ns tf(SCK) Down 30pF timing Ducy (SCK) Slave Input Clock 70 % modal 30 Duty Cycle tsu(NSS) 4tPCLCK **NSS** Establishment modal Time 2tPCLCK $th \left(NSS\right)^{(2)}$ NSS Hold Time modal tw(SCKH (2 Master mode, fPCLK = SCK high and low 50 60 36MHz, preshunt tw(SCKL)⁽²⁾ time factor = 4 $tsu(MI)^{(2)}$ Master Mode 5 Data Entry tsu(SI) (2) Establishment Time, modal 5 ns Main paradigm CKS32F103x8 and CKS32F103xB, a series of 32-bit MCUs Data Entry Hold Time, Semiconductor Manufacturing Corp. Master Mode 5 Semiconductor Manufacturi th(SI)⁽²⁾ Main 4 modal paradigm

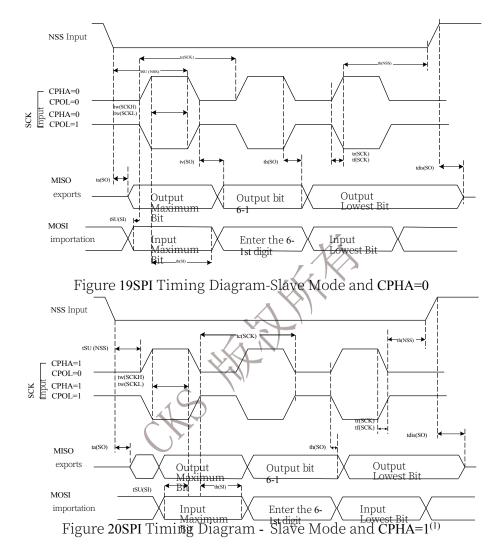
Slave mode, $_{fPCLK} = 20MHz$

3tPCLCK

0

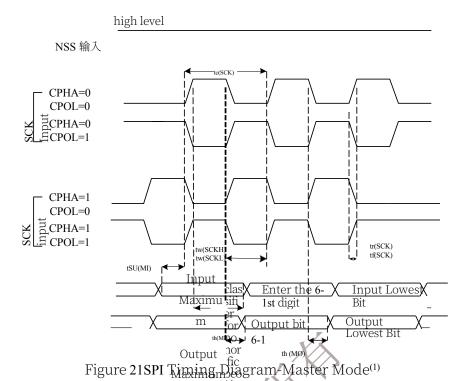


- 1. The SPI1 characterization of the remapping needs to be further determined.
- 2. Derived from a comprehensive assessment and not tested in production.
- 3. The minimum value indicates the minimum time to drive the output, and the maximum value indicates the maximum time to get the data correctly.
- 4. The minimum value indicates the minimum time to turn off the output, and the maximum value indicates the maximum time to place the data line in a high resistance state.



1. The measurement points are set at CMOS levels: 0.3VDD and 0.7VDD.





1. The measurement points are set at CMOS level\$i@.3VDD and 0.7VDD.

USB Characteristics

The USB (Full Speed) interface is

Table 40USB Startup Time

notation parameters maximum unit (of values measure)

1. Guaranteed by designs, thet USB Transceiver 1
tested in production. Startup Tine 1
notation parameters prefer USB DC Characteristics

			touture Time			
teste	in product notation	parameters	tartup Tipe 1USB DC Ch prerequisite	aracteristic Minimum	cs (Maximum	unit (of
				1)	value (1)	measur
						e)
	Input lev	el				
	VDD	USB Operating		3.0(3)	3.6	V
		Voltage ⁽²⁾				
	VDI (4)	Differential	I(USBDP,USBDM)	0.2		
		Input Sensitivity				\rfloor V
	VCM ⁽⁴⁾	Differential	Includes _{VDI} scopes	0.8	2.5	
1. All volt	age measur	common mode ements are based on	the ground at the equipmen	t end.		

- 2. For compatibility with the USB 2.0 full-speed electrical specification, the USBDP (D+) pin must be connected to a voltage of $3.0 \sim 3.6 \text{V}$ through a 1.5k Ω resistor.
- 3. The correct USB functionality of the CKS32F0103xx is guaranteed at 2.7V instead of the degraded electrical characteristics in the 2.7~3.0V voltage range.

CKS32F103: Semicond	ĸ8 an ∀Œĸs32F uctor Manufa	193½H ièsGiftSpff€2-bit cturing Corp. low level	MCV:5fronRL to 3.6V(5)		0.3	V
	VOH	Static Output High	15kΩ RL to V ⁽⁵⁾ ss	2.8	3.6	

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- 4. Assured by comprehensive evaluation, not tested in production.
- 5. RL is the load connected to the USB drive.

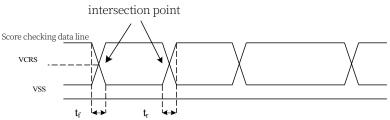


Figure 22USB Timing: Data Signal Rise and

Fall Time Definitions Table

notation	parameters	conditional 2USB Full Speed E	minimum lectrical	maximum values	unit (of measure)
			varue	varues	measure)
tr	rising time ⁽²⁾	CL≤50pF Characteristics ⁽¹⁾	4	20	ns
tf	descent time ⁽²⁾	CL ≤ 50pF	4	20	ns
trfm	Rise and fall time	tr / tf	90	110	%
	matching				
VCRS	Output Signal Cross		1.3	2.0	V
	Voltage		VA		

- 1. Guaranteed by design, not tested in production.
- 2. Measurement data signal from 10% to 90%.

5.3.16 CAN (Controller Area Network) interface

See Section 5.3.12 for details on the characteristics of the input/output multiplexing function pins (CAN_TX and CAN_RX).

5.3.17 12-Bit ADC Characterization

Unless otherwise noted, the parameters in Table 43 are measured using ambient temperature, $_{\text{fPCLK2}}$ frequency, and $_{\text{VDDA}}$ supply voltage that meet the conditions in Table 6.

NOTE: It is recommended that a calibration be performed at each power-up.

	Table 43ADC Characteristics						
	notation	parameters	conditional	minimum	typical	maximu	unit (of
				value	value	m	measur
						values	e)
	VDDA	Supply Voltage	-	2.4	-	3.6	V
	VREF+	Positive reference	-	2.4	-	VDDA	V
		voltage					
CKS32	IVREF F103x8 and C	Voltage at V input pin (\$32F103xB, a series of 32-bit MC	Us from	-	160(1)	220(1)	μΑ
		n ADC COCKFrequency	-	0.6	-	14	MHz
	fS (2)	sampling rate	-	0.05	-	1	MHz
	(2)	External Trigger	fADC=14MHz	-	-	823	kHz
	fTRIG ⁽²⁾	External Higger				1.7	1/fADC

Datasheet



sneet .						
VAIN ⁽³⁾	Conversion voltage	-	0 (vssa or vref-	-	VREF+	V
	range		Connect to			
	range		ground)			
RAIN (2)	External Input		-	-	50	kΩ
	Impedance					
RADC ⁽²⁾	Sampling Switch		-	-	1	kΩ
	Resistor					
CADC ⁽²⁾	Internal sample and				8	pF
	hold capacitance					
(2)	calibration time	fADC=14MHz		5.9	•	μs
tC AL	Cambration time		83			1/fADC
(2)	Injection Trigger	fADC=14MHz			0.214	μs
tla t ⁽²⁾	,				3(4)	1/fADC
	Conversion Delay					
tla tr	Regular Trigger	fADC=14MHz			0.143	μs
tia tr 1	Transition Delay				2(4)	1/fADC
	Transmon Delay	21.5.2.1.5.55				
ts ⁽²⁾	sampling time	fADC=14MHz	0.107		17.1	μs
			1.5		239.5	1/fADC
tSTAB (2)	power-on time		0	0	1	μs
tCONV ⁽²⁾	Total conversion	fADC=14MHz	1		18	μs
tCONV`'	time		14~252 (samp	oling tS+		1/fADC
	(including		progressively approaching		hing	
	sampling time)		12.5)			

- 1. Assured by a comprehensive assessment, not tested in production.
- 2. Guaranteed by design, not tested in production.
- 3. In QFN36, LQFP48, and LQFP64 packages, v_{REF+is} internally connected to v_{DDA} and v_{REF-is} internally connected to v_{SSA} . see Table 2 for details.
- 4. For external triggering, a delay 1/IPCLK2 must be added to the delays listed in Table 43.

Formula 1:

Maximum RAIN

$$_{\text{RAIN}} < \frac{\text{TS}}{f_{\text{ADC}} \times C_{\text{ADC}} \times \text{In}(2N+2)}$$
 - RADO

Formula

The above equation (Equation 1) is used to determine the maximum external impedance that will allow an error of less than 1/4 LSB, where N=12 (for 12-bit resolution).

Table 44fADC = Maximum RAIN at 14MHz (1)

	1 abic 441A	DC WIGHTINGTH KAIN	AC 1 11V1112
	тs (cycle)	t _S (μs)	Maximum $_{RAIN}(k\Omega)$
	1.5	0.11	0.4
	7.5	0.54	5.9
CKS32F103x8 and CKS32F103	хв, a series 3f \$2-bit MC	Us from 0.96	11.4
Semiconductor Manufactu		2.04	25.2
	41.5	2.96	37.2
	55.5	3.96	50

CKS32F103x8 and CKS32F103xB Datasheet



1. Guaranteed by design, not tested in production.

1. The I

1. The D



Table 45ADC Accuracy - Restricted Test Conditions(1)(2)

_								
	notatio n	parameters	test condition	typical value	Maximu m value	unit (of		
					(3)	meas		
						ure)		
	ET	Aggregate error	- 57 MIL-	±1.3	±2			
	ЕО	offset error	_{fPCLK2} = 56 MHz	±1	±1.5			
D D	E G C accura	cy væde of the ADC	_{fADC} = 14 MHz, RAIN< 10 kΩ, _{VDDA} is measure g a ften an int ern accalibration	n. ±0.5	±1.5	LSB		
- 1			1 3 3 3 V 1 A 2 2 3 C					

2. ADC Accuracy vs. Referential ent Injection: It is important to avoid injecting verse cuttent on any standard analog input pin, linear entropy ignificantly degrade the accuracy of a conversion being performed after ADC calibration analog input pin. It is referenced that a Schottky diode be added to the standard analog pin (between the pin and ground) where rentest aljection current may be generated.

±0.8 ±1.5

The ADC accuracy wear Hyt Exercised if the forward injection current, as long as it is within the INJUENN) and EINJUENN ranges given in Section 5.3.12.

3. Assured by comprehensive evaluation, not tested in production.

Table 46ADC Accuracy(1)(2)(3)									
notatio	parameters	test condition	typical	Maximu	unit				
n			value	m value	(of				
				(3)	meas				
					ure)				
ET	Aggregate error		±2	±5					
ЕО	offset error	$_{\rm fPCLK2}$ = 56 MHz $_{\rm fADC}$ = 14 MHz, RAIN< 10 k Ω , $_{\rm VDDA}$	±1.5	±2.5					
EG C. accurac	gain error	s measured aft@i4ar3i6Vernal calibrati	±1.5	±3	LSB				
, EDc	differential		±1.	±2					

2. Optimal performance can be achieved exercise the tree frequency of the performance can be achieved exercised the frequency of the performance can be achieved exercised to the performance can be achieved to the performa

3. ADC Accuracy vs. Reverse current Injection: It is important to avoid injecting reverse current on any standard after ADC calibration analog input pin, as this can significantly degrade the accuracy of a conversion being performed on another analog input pin. It is recommended that a Schottky diode be added to the standard analog pin (between the pin and ground) where nearly injection current may be generated.

The ADC accuracy will not be affected if the forward injection current, as long as it is within the $_{IINJ(PIN)}$ and $_{\Sigma IINJ(PIN)}$ ranges given in Section 5.3.12.

4. Assured by comprehensive evaluation, not tested in production.



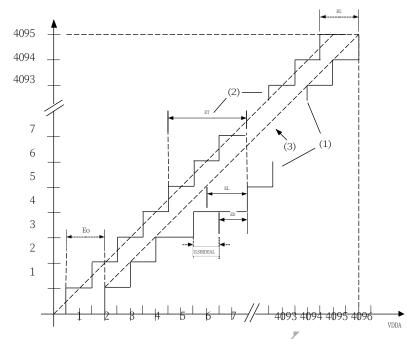


Figure 23ADC Accuracy Characteristics

- (1) Example of an actual ADC conversion curve
- (2) Ideal Conversion Curve
- (3) Actual conversion point connection

ET Combined error: the maximum deviation between the actual conversion curve and the ideal conversion curve.

Eo offset error: the difference between the first leap on the actual conversion curve and the first leap on the ideal conversion curve.

EG Gain error: the difference between the last leap on the actual conversion curve and the last leap on the ideal conversion curve.

 $_{\rm ED}$ Differential Linearity Error: The difference between the actual step on the conversion curve and the ideal step (1LSB). Where 1LSBIDEAL=VREF+/4096 (or VDDA/4096, depending on the package)

EL Integral linearity error: Maximum deviation of the actual conversion curve from the endpoint line.

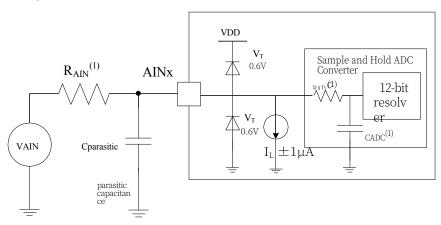


Figure 24 Typical Connection Diagram Using ADCs

1. See Table 46 for RAIN, RADC, and CADC values.

CKS32F103x8 and CKS32F103xB



2. Cparasitic represents the parasitic capacitance (about 7pF) of the PCB (related to the quality of soldering and PCB layout) with respect to the pads. Larger Cparasitic values will reduce the accuracy of the conversion and the solution is to reduce the fadc.



PCB Design Recommendations

Depending on whether $_{VREF+\,is}$ connected to $_{VDDA}$ or not, the decoupling of the power supply must be connected according to Figure 25 or Figure 26. The 10nF capacitors shown must be dielectric capacitors and should be placed as close as possible to the MCU chip.

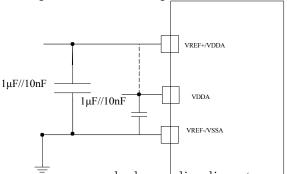


Figure 25 Supply and reference \overline{p} ower supply decoupling lines (vREF+ not connected to vDDA)

 $1.\,_{\text{VREF+}}$ and $_{\text{VREF-}}$ inputs are only found on products with 100 feet or more.

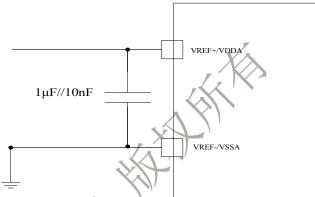


Figure 26 Supply and reference power supply decoupling lines ($_{VREF^+}$ connected to $_{VDDA}$) 1. The $_{VREF^+}$ and V $_{REF^-}$ inputs are only found on products with more than 100 pins.

5.3.18 Temperature Sensor Characteristics

Table 47 Temperature Sensor Characteristics

	notation	parameters	minimum	typical	maximu	unit (of
			value	value	m values	measur
						e)
	(1) TL	vsense Linearity with respect to		±1	±2	° C
		temperature				
	Avg_Slope ⁽¹⁾	average slope	4.0	4.3	4.6	mV/°C
1. Assı	ured bygomprehe	nsive evalu atiohtapetaested in producti	on. 1.61	1.62	1.63	V
2. Gua	rant ęg laky design	, not test ed tallife have are time	4		10	μs
3. The	minimum(2%2mpli	ng ti ndcasamphingninne by klen appli	cation progr	am through	mul ţip ile cyc	les.µs
		reading temperature				



6. Package Characteristics

6.1 Encapsulated mechanical data

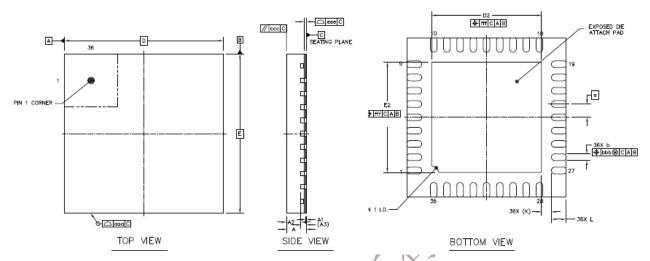


Figure 27QFN36 Package Diagram

Table 48QFN36 Package Mechanical Data

grade	.41	millimetre		
grade	minimum	typical value	maximum	
	value		values	
A	0.70	0.75	0.80	
A1	0	0.02	0.05	
A3		0.203 REF		
b	0.20	0.25	0.30	
D		6 BSC		
Е		6 BSC		
e		0.5 BSC		
D2	4.05	4.15	4.25	
E2	4.05	4.15	4.25	
K		0.375 REF		
L	0.45	0.55	0.65	
aaa		0.1		
ccc	0.1			
eee	0.08			
bbb	0.1			
fff		0.1		



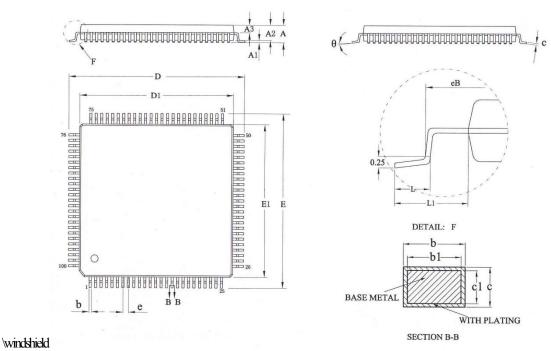


Figure 28LQFP100, 100-pin low-profile

square flat package diagram Table

arothi OEI	millimetre P 100, 100-pin low-profile square flat					
granneQFF	minimum	typical value	maximum			
	valpackas	ge data	values			
A			1.60			
A1	0.05	-	0.15			
A2	1.35	1.40	1.45			
A3	0.59	0.64	0.69			
b	0.18	-	0.26			
b1	0.17	0.20	0.23			
c	0.13	-	0.14			
D	15.80	16.00	16.20			
D1	13.90	14.00	14.10			
Е	15.80	16.00	16.20			
E1	13.90	14.00	14.20			
eB	15.05	-	15.35			
e		0.50BSC				
L	0.45	-	0.75			
L1		1.00REF				
θ	0	-	7°			



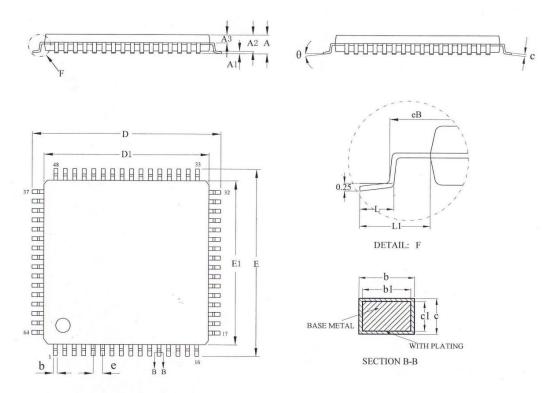


Figure 29 LQFP64, 64-pin low-profile

square flat package diagram Table 50

gradeFP64		millimetre				
81 42(9) FP64	, 64-pin low-pi minimum	rofile square f typical value	maximum			
nackag	value e data		values			
— packag A	-	-	1.60			
A1	0.05	-	0.15			
A2	1.35	1.40	1.45			
A3	0.59	0.64	0.69			
b	0.18	-	0.26			
b1	0.17	0.20	0.23			
c	0.13	-	0.17			
D	11.80	12.00	12.20			
D1	9.90	10.00	10.10			
Е	11.80	12.00	12.20			
eB	11.25	-	11.45			
E1	9.90	10.00	10.10			
e		0.50BSC				
θ	0°	-	7°			
L	0.45	-	0.75			
L1		1.00REF				



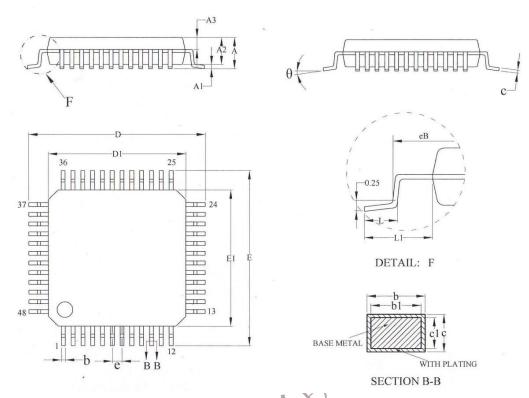
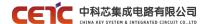


Figure 30LQFP48, 48-pin low-profile

square flat package Diagram 51LQFP48,

gradonin	millimetre		
grææpin	minimum	uare flat pack typical value	maximum
data	value		values
A	_	-	1.60
A1	0.05	-	0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
b	0.18	-	0.26
b1	0.17	0.20	0.23
c	0.13	-	0.17
c1	0.12	0.13	0.14
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
Е	8.80 9.00		9.20
E1	6.90 7.00 7		7.20
eB	8.10 - 8.25		8.25
e	0.50BSC		
L	0.40	-	0.65



L1	1.00REF		
k	0	-	7°

6.2 thermal property

The maximum junction temperature (TJmax) of the chip must not exceed the range of values given in Table 6.

The maximum junction temperature (TJmax) of the chip is expressed in Celsius and can be calculated by the following formula:

$$TJmax = TAmax + (PDmax \times \Theta JA)$$

Among them:

- TAmax is the maximum ambient temperature, expressed in °C.
- _{OJA} is the thermal impedance of the junction to ambient in the package, labeled in °C/W.
- PDmax is the sum of PINTmax and PI/Omax (PDmax = PINTmax + PI/Omax).
- PINTmax is the product of IDD and VDD, expressed in watts, and is the maximum internal power consumption of the chip.

PI/Omax is the maximum power consumption of all output pins:

$$PI/Omax = \Sigma(VOL \times IOL) + \Sigma((VDD - VOH) \times IOH).$$

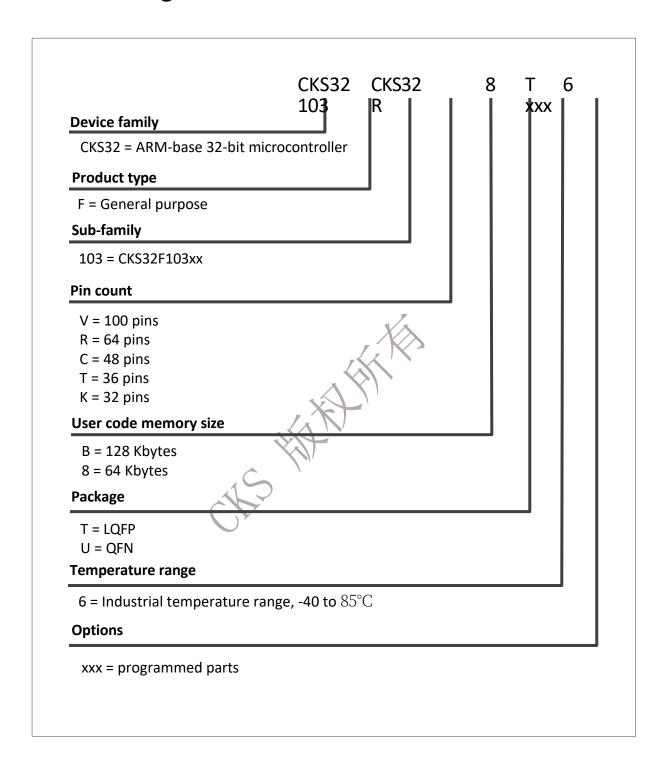
Consider the actual VOL/IOL and VOH/IOH that are low and high on the I/O in the application.

Table 52 Thermal Characteristics of Packages

	Tuble 52 Thermal Gharacteriongs of Facinages					
	notatio	parameters	numerical	unit		
	n		value	(of		
				measu		
		19		re)		
		Thermal Impedance to Environment - LQFP100 -	46			
	ΘЈА	14×14mm/0.5mm Pitch		9C /W		
6.2.1	reference documentnce of Junction to Environment - 45					
		LQFP64 - 10×10mm/0.5mm Pitch				
JE	SD51-2 En	vTibermentur poddusere for Thiemtal Mexisurements of Integested Circuits-Natur			itural	
С	onvection	(AQFR48-57) 7500 (W.W. Pitchorg				
		Thermal impedance of junction to environment -	18			
		QFN36-6×6mm/0.5mm pitch				



7. Model Naming





8. Version History

dates	releases	revised part
2018.01.18	Initial draft	
2018.04.20	1.0	Modify the pin definitions for pin 80 and pin 81 in Figure 3;
		Typical values with 48MHz clock are added in Table 14;
		Add Table 15 Typical Current Consumption in Run Mode,
2018.08.11	1.1	Data Processing Code from Internal
		Running in RAM ;
		Modify the clock in Table 16 to the typical value at
		72MHz;
		Revise the maximum value
2018.10.10	1.2	of _{fLSE_ext} in Table 18; revise
		the _{IDD} unit μA to mA in Table
		26;
		Modify the minimum, typical, and maximum values
		for v ₂₅ in Table 47.
2018.10.15	1.3	Add sections on device comparison/ordering
		information/model designation, etc.
2020.03.17	1.4	Added package QFN36 related content